

# *Principles of Micro- and Nanofabrication for Electronic and Photonic Devices*

## Introduction

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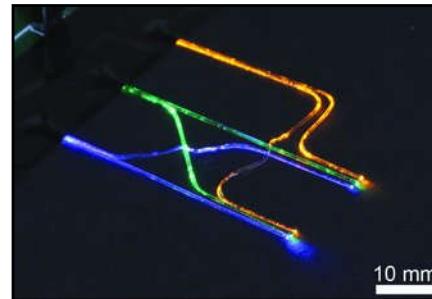
# Optical and Electronic Devices



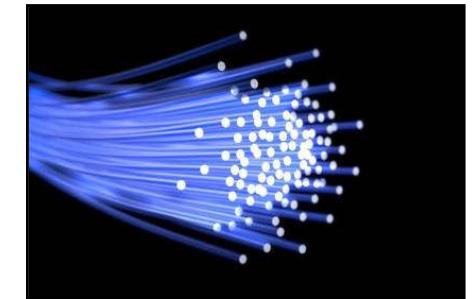
LEDs



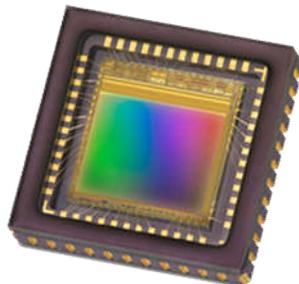
lasers



waveguides



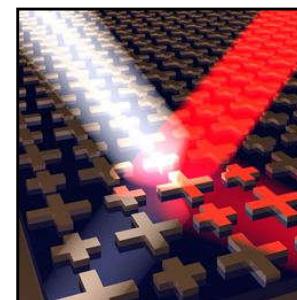
fibers



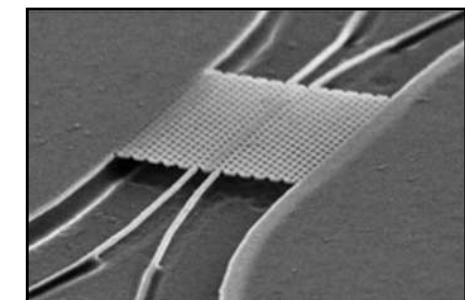
detectors



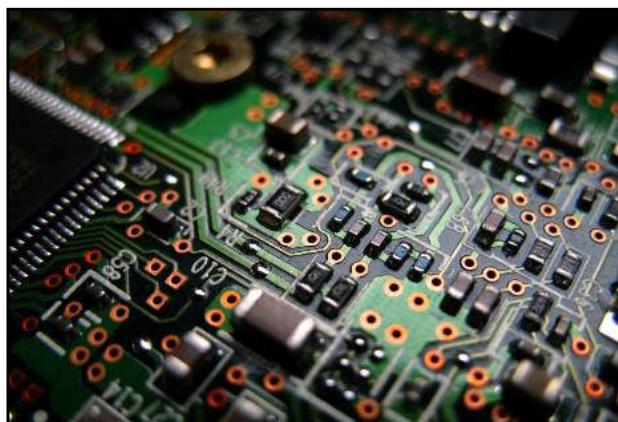
solar cells



metamaterials



photonic crystals



integrated circuits

Airflow  
SensorsCurrent  
SensorsFiber Optics and  
Liquid Level SensorsHumidity  
Sensors

Infrared Sensors

Magnetic  
Sensors

Flexible Heaters



Force Sensors

Proximity  
SensorsRotary Position  
SensorsSpeed  
Sensors

# Goal of This Course

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- Focus on the **fabrication and processing methods** to form electronic and optical devices at micro- and nano-scale
- Cover fundamental concepts to **grow, pattern, deposit, etch and integrate** various materials (silicon, III-V, etc) to form electronic and optical devices
- **Emerging fabrication technologies** such as nanofabrication and self-assembly will also be included

# Nobel Prize in Physics

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- 1956      **Semiconductor transistors**
- 1991      **Liquid crystals**
- 2000      **Integrated circuits**
- 2000      **Semiconductor heterostructures**
- 2009      **CCD imaging sensors**
- 2009      **Optical fibers**
- 2010      **Graphene**
- 2014      **GaN based blue LEDs**

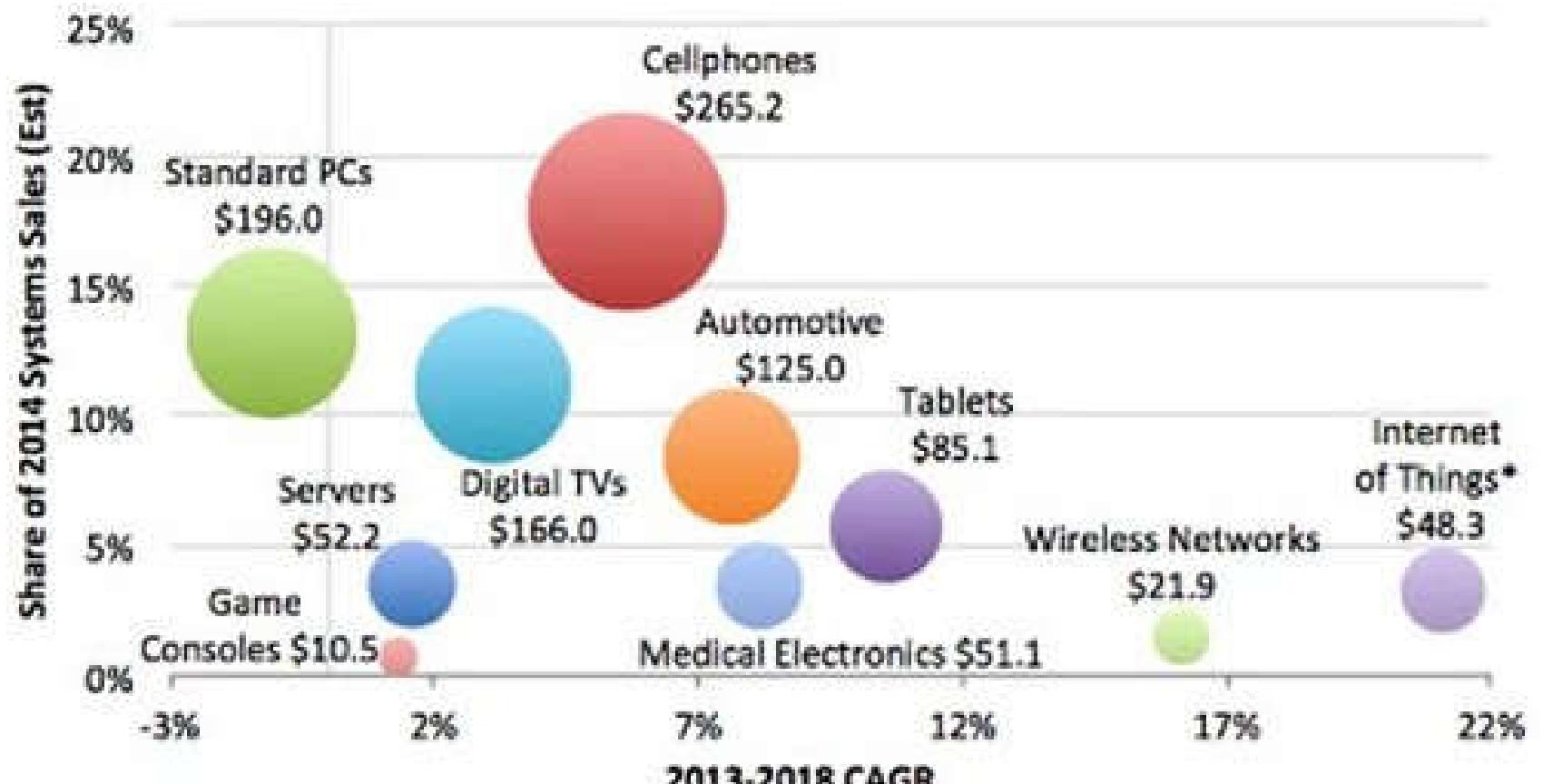
# 'Disruptive' Technologies

- 1956      **Semiconductor transistors**      ← **vacuum tubes**
- 1991      **Liquid crystals**      ← **CRT displays**
- 2000      **Integrated circuits**
- 2000      **Semiconductor heterostructures**
- 2009      **CCD imaging sensors**      ← **film cameras**
- 2009      **Optical fibers**      ← **copper cables**
- 2010      **Graphene**
- 2014      **GaN based blue LEDs**      ← **incandescent light bulbs**

# Semiconductor Market

current ~ 500 billion \$\$\$

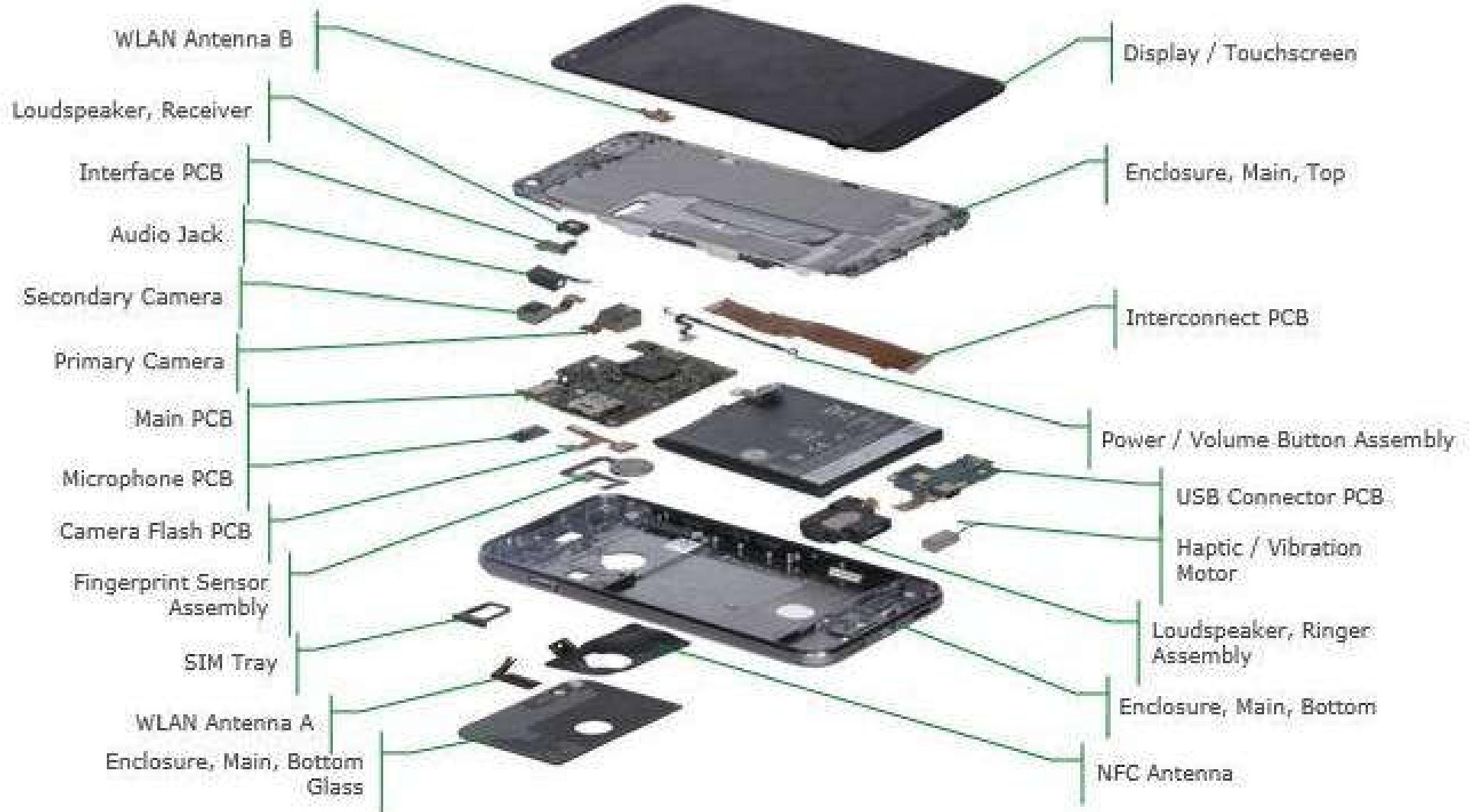
GDP of Thailand: 400 billion \$\$\$



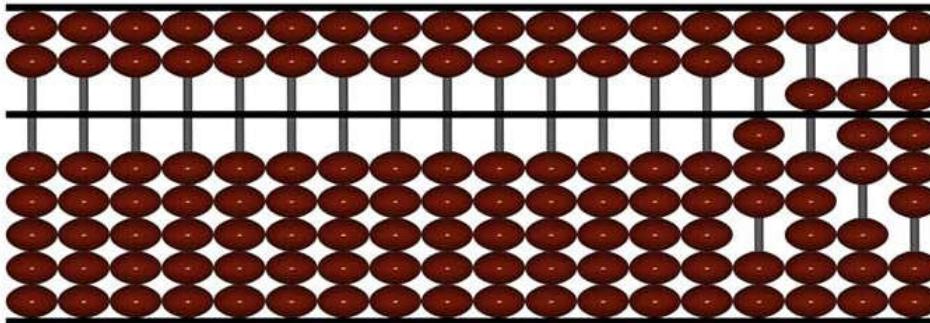
\*Covers only the Internet connection portion of systems

Source: IC Insights

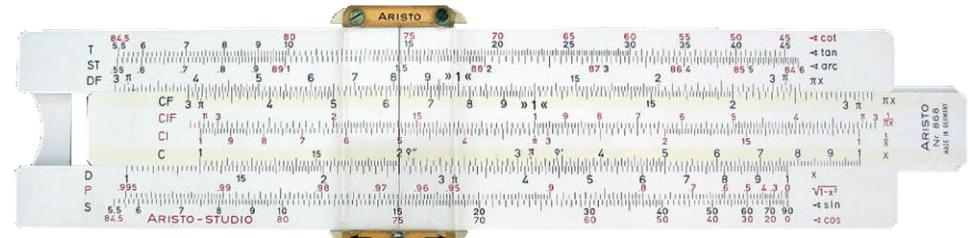
# Devices in a Smartphone



# Some 'Ancient' Computers

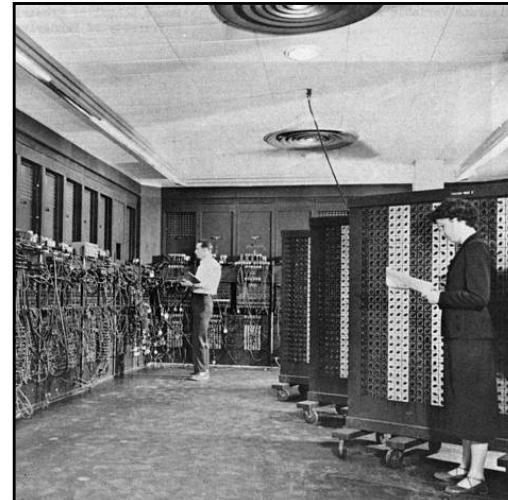


abacus



slide rule

- First 'electronic' computer
  - ENIAC, 1943
  - 30 tons, 200 kW
  - 18000 vacuum tubes
  - 5000 times/sec
  - cost \$480,000

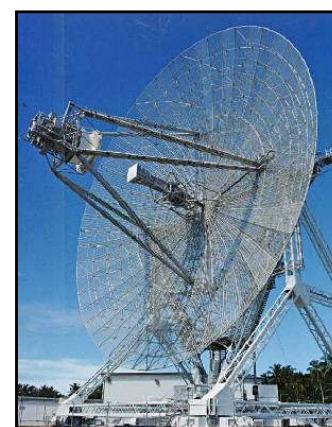
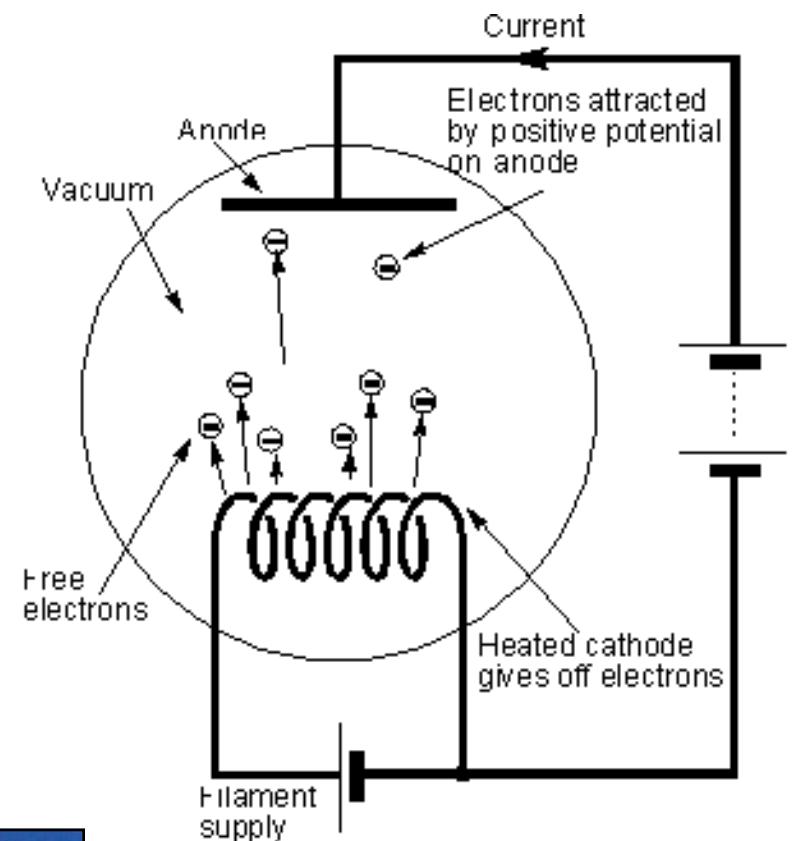


vacuum tube

# Vacuum Tube

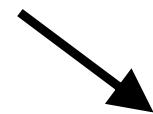


current flows only in one direction: **diode**



# First Semiconductor Transistor

Germanium  
Bipolar Transistor



*The first point contact transistor*  
William Shockley, John Bardeen, and Walter Brattain  
Bell Laboratories, Murray Hill, New Jersey (1947)

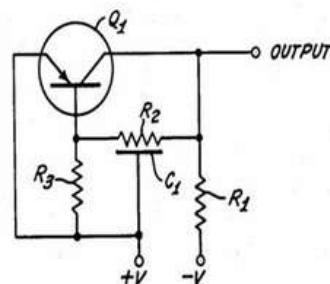
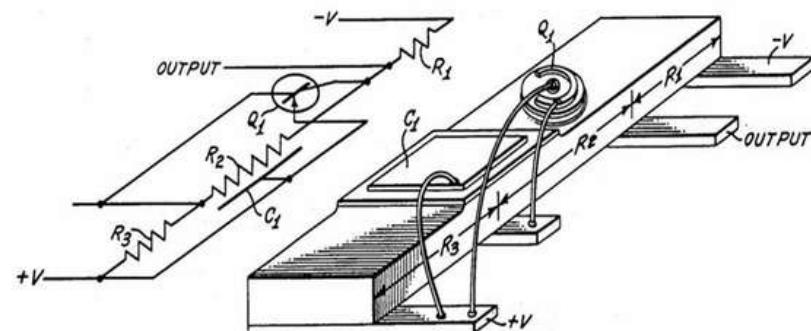


1956 Nobel Prize in Physics

# First Integrate Circuits

## The First (2D) Integrated Circuit Jack Kilby, Texas Instruments, 1958

- Transistor, Resistors and Capacitors on the same piece of semiconductor
- **Interconnects between components not integrated**  
→ Low connectivity between components



Germanium



J. Kilby  
1923–2005

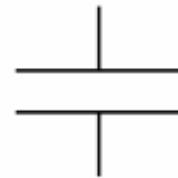
**Q: Why Ge?**

**2000 Nobel Prize in Physics**

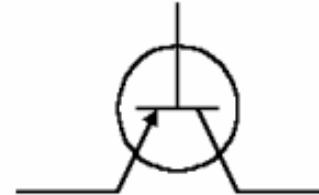
# First Integrate Circuits



diode



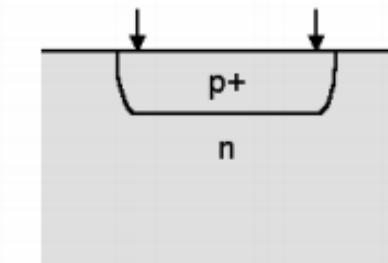
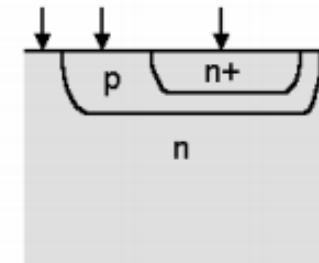
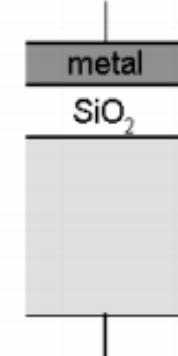
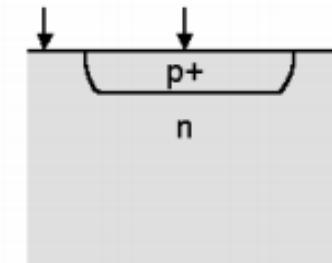
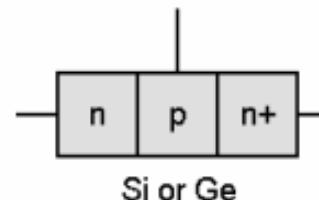
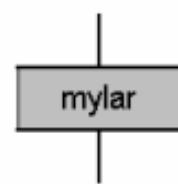
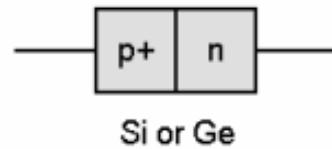
capacitor



transistor



resistor



**All devices can be made in the same semiconductor!**

# First Integrate Circuits

**"There is plenty of room at the bottom", APS Meeting, 1959**

## MINIATURIZING THE COMPUTER

I don't know how to do this on a small scale in a practical way, but I do know that computing machines are very large; they fill rooms. Why can't we make them very small, make them of little wires, little elements—and by little, I mean *little*. For instance, the wires should be 10 or 100 atoms in diameter, and the circuits should be a few thousand angstroms across. Everybody who has analyzed the logical theory of computers has come to the conclusion that the possibilities of computers are very interesting—if they could be made to be more complicated by



R. Feynman

# First Integrate Circuits

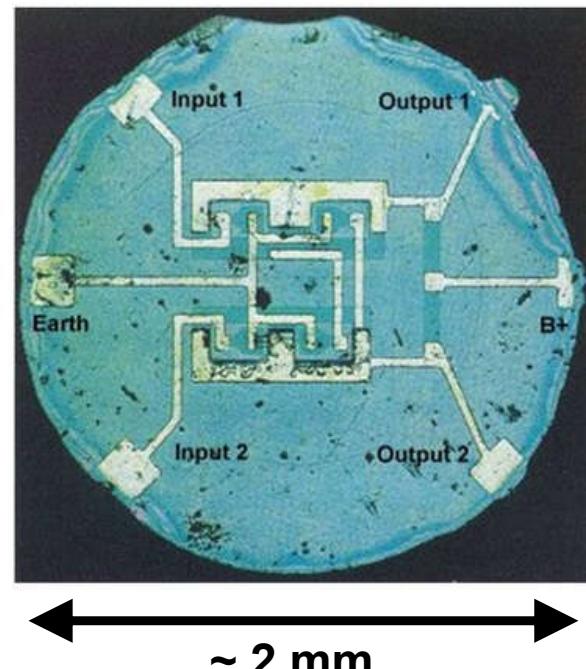
The First **Monolithic** (2D) Integrated Circuit

**Robert Noyce, Fairchild Semiconductor, 1961**

- Transistor, Resistors and Capacitors on the same piece of semiconductor
- **Interconnects between components integrated**  
→ High connectivity between components

**Silicon**

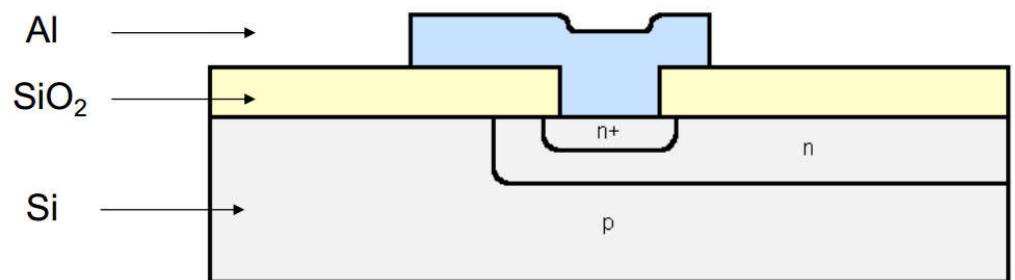
**4 transistors**



**R. Noyce  
1927–1990**

# First Integrate Circuits

- Thermal oxidation ( $\text{SiO}_2$ )

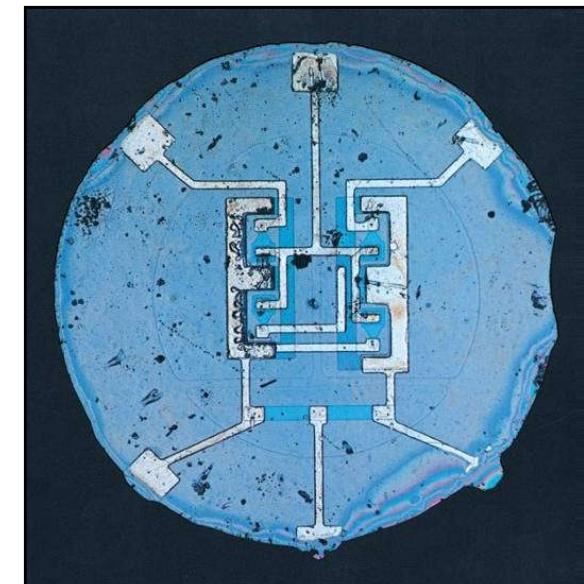


- Photolithography

- Etching

- Thermal diffusion (n-Si, p-Si)

- Metal deposition (Al)

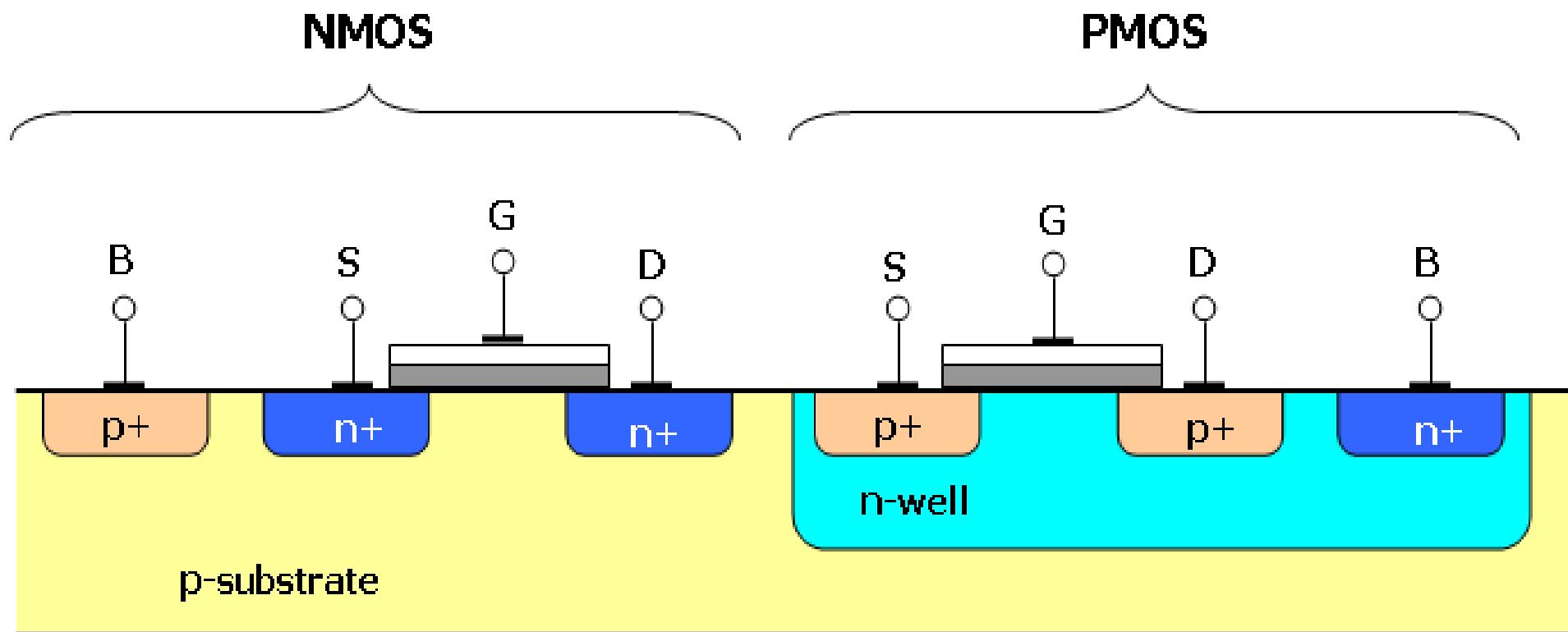


***Very similar to today's process***

↔ ~ 2 mm

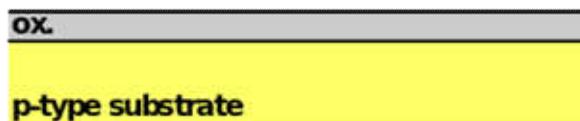
# CMOS

- Complementary Metal-Oxide-Semiconductor
  - F. Wanlass, Fairchild, 1963

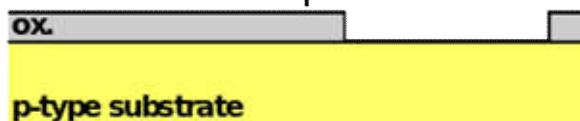


# CMOS Process

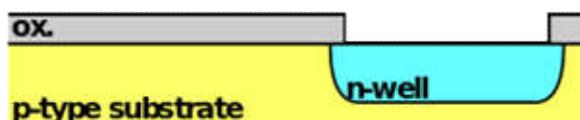
1. Grow field oxide



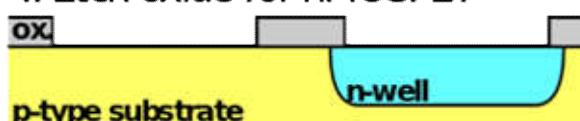
2. Etch oxide for pMOSFET



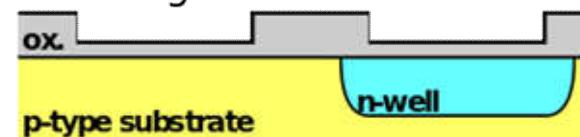
3. Diffuse n-well



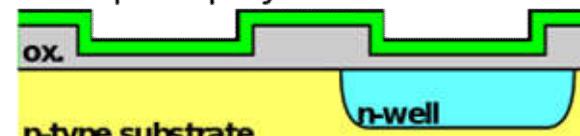
4. Etch oxide for nMOSFET



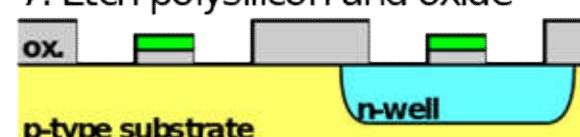
5. Grow gate oxide



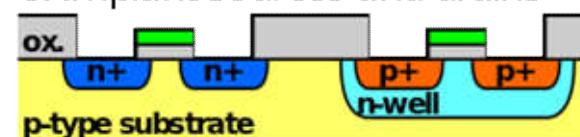
6. Deposit polysilicon



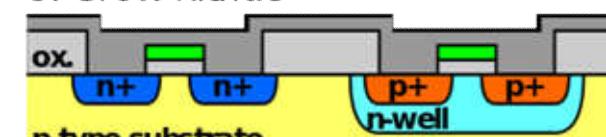
7. Etch polysilicon and oxide



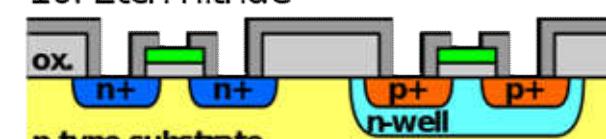
8. Implant sources and drains



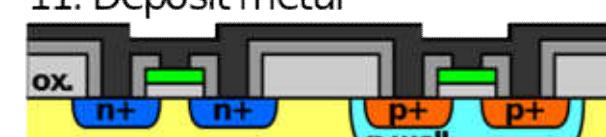
9. Grow nitride



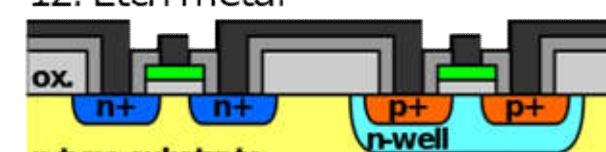
10. Etch nitride



11. Deposit metal

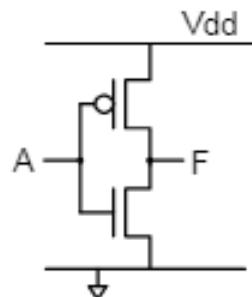


12. Etch metal



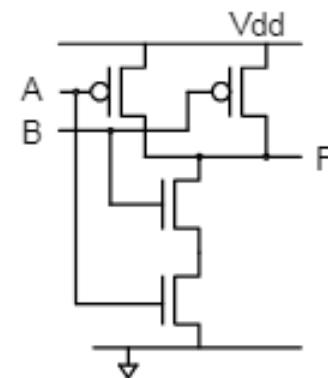
[Video](#)

# CMOS Logic



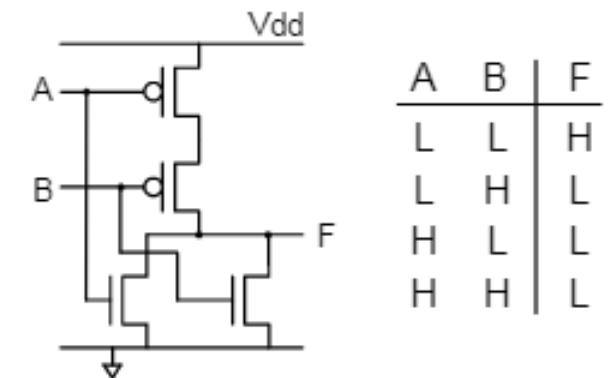
CMOS INVERTER

A	F
L	H
H	L



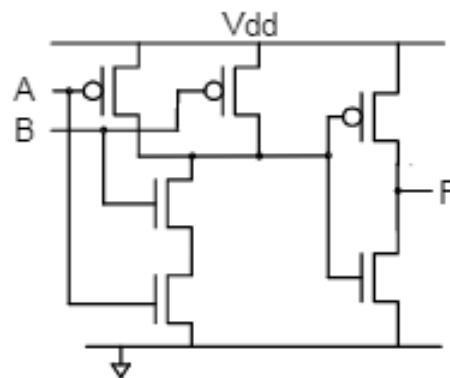
CMOS NAND

A	B	F
L	L	H
L	H	H
H	L	H
H	H	L



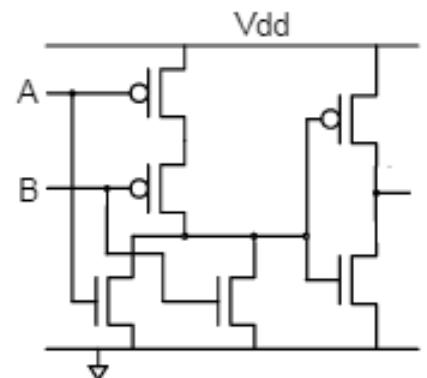
CMOS NOR

A	B	F
L	L	H
L	H	L
H	L	L
H	H	L



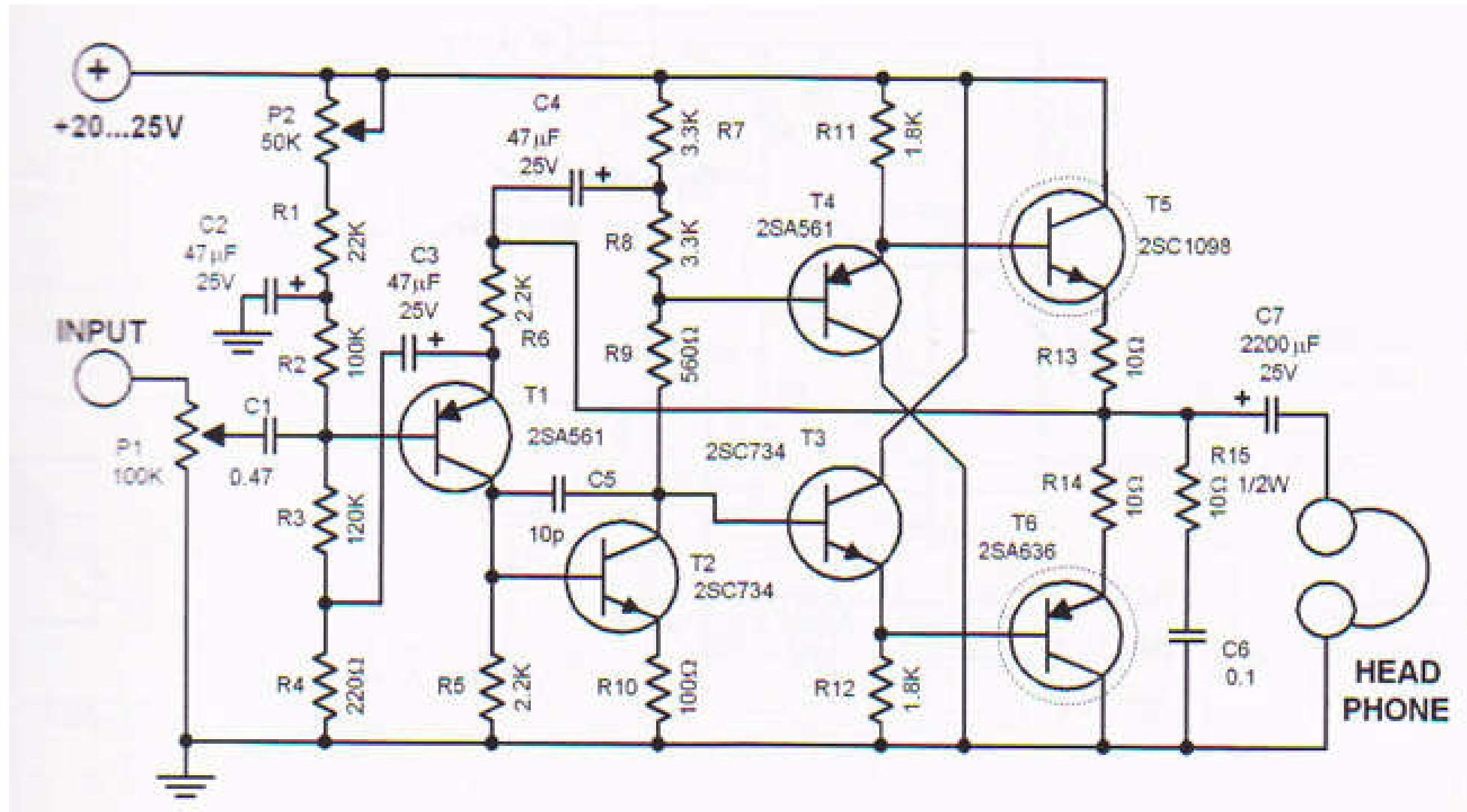
CMOS AND

A	B	F
L	L	L
L	H	L
H	L	L
H	H	H



CMOS OR

# CMOS Circuit

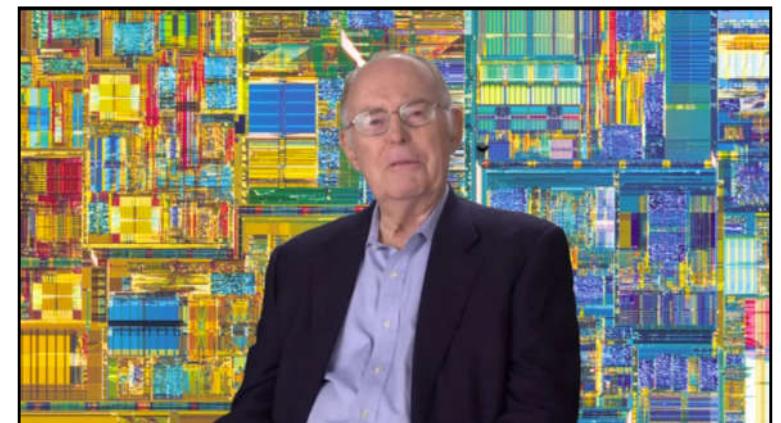


# Integrate Circuits

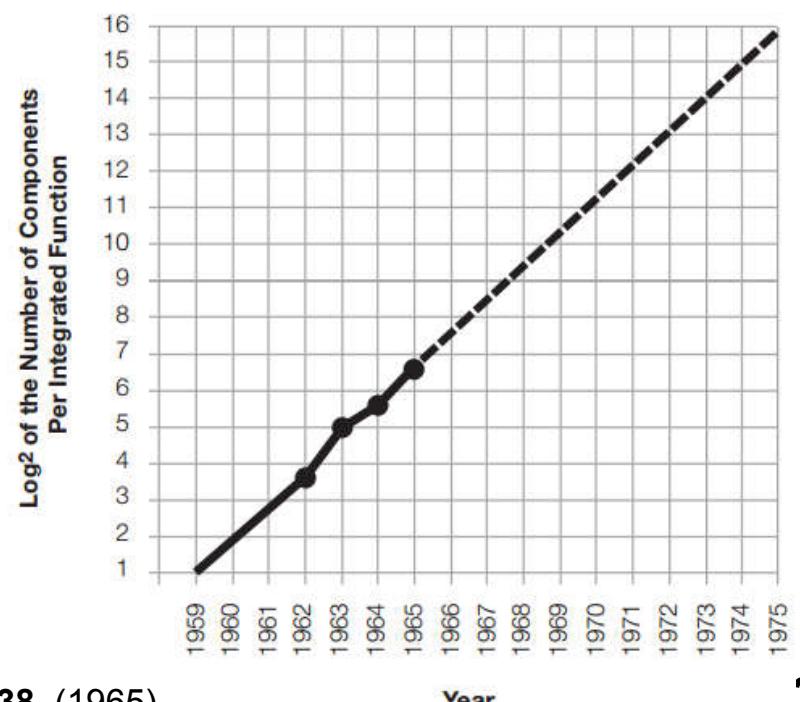
- **Moore's law, Fairchild, 1965**

The complexity for minimum component costs has increased at a rate of roughly a factor of two per year (see graph on next page). Certainly over the short term this rate can be expected to continue, if not to increase. Over the longer term, the rate of increase is a bit more uncertain, although there is no reason to believe it will not remain nearly constant for at least 10 years. That means by 1975, the number of components per integrated circuit for minimum cost will be 65,000.

I believe that such a large circuit can be built on a single wafer.



**G. Moore**



# Integrate Circuits

- Moore's law, Fairchild, 1965

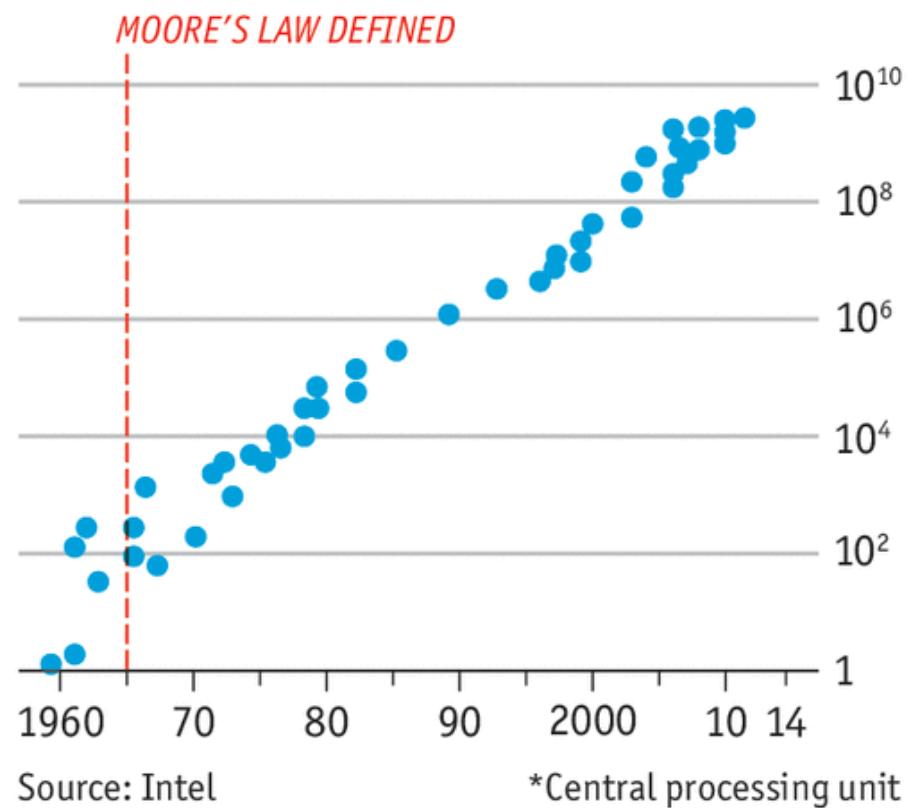


G. Moore



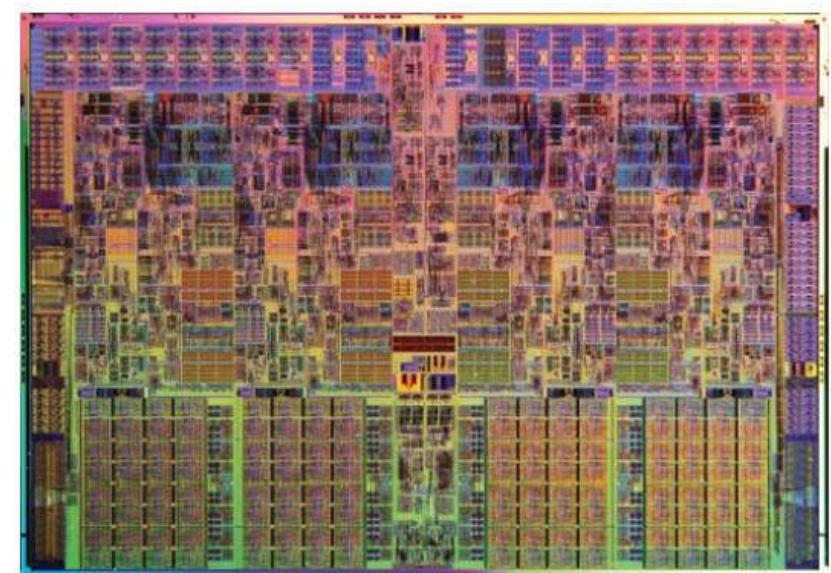
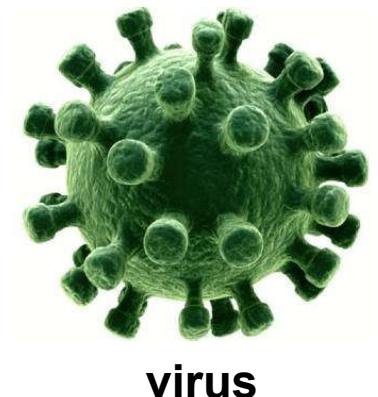
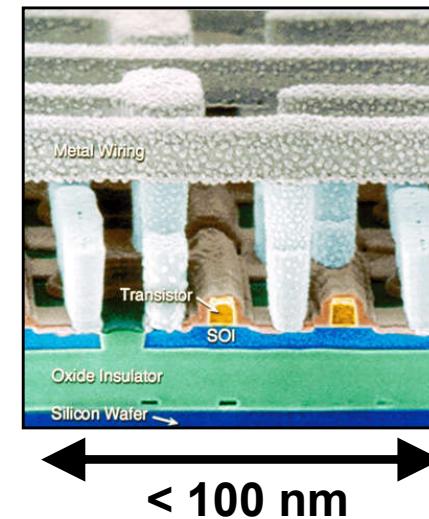
# Integrate Circuits

- Moore's law, Fairchild, 1965



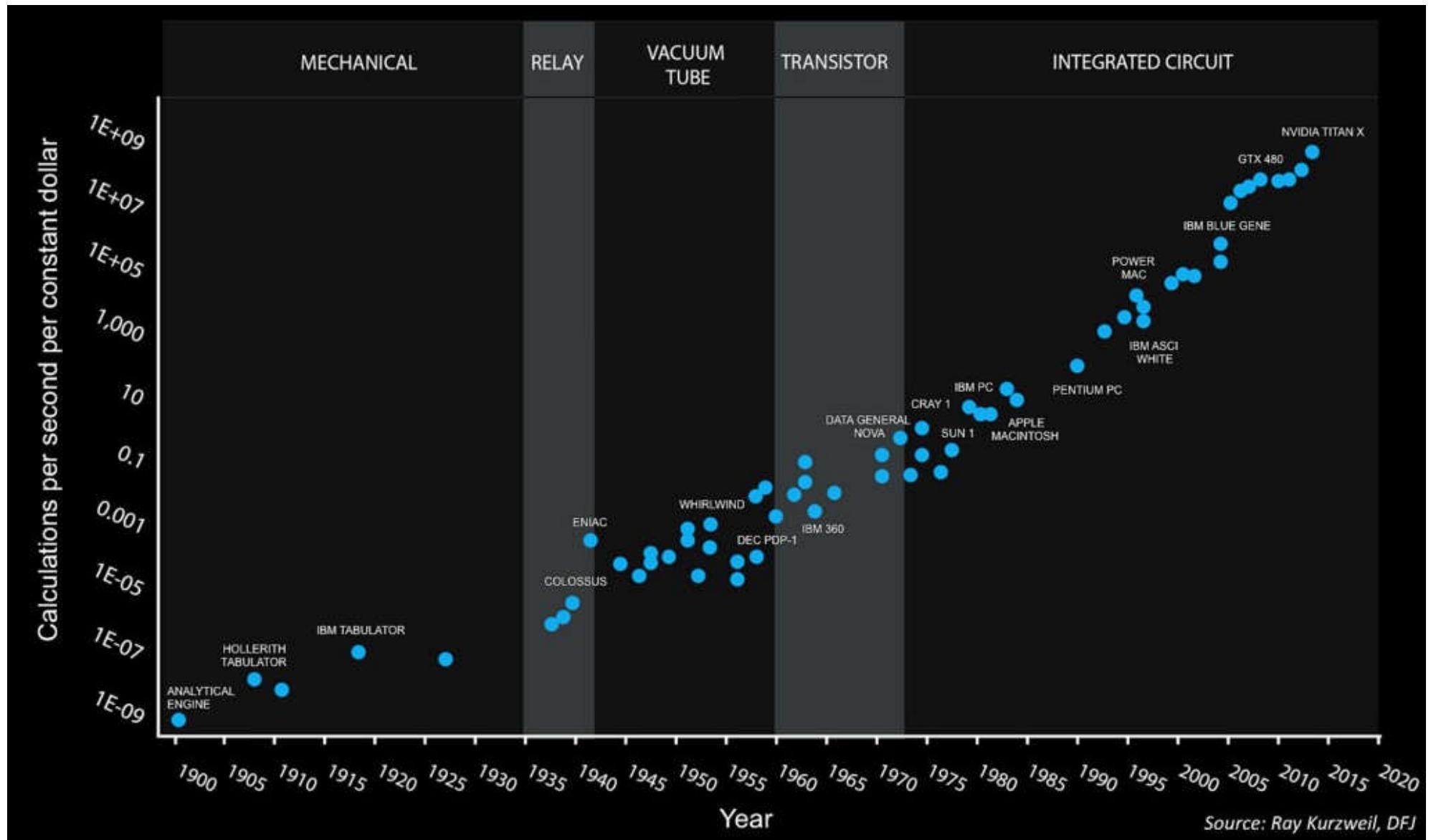
Economist.com

***Modern Electronics is a  
real Nanotechnology***



**Intel i7 CPU,  $\sim 10^9$  transistors**

# 120 Years of Moore's Law



# Integrate Circuits

**the 10-Megabyte Computer System**



**Only \$5995 COMPLETE**

**New From IMSAI**

- 10 Megabyte Hard Disk
- 5 1/4" Dual-Density Floppy Disk Back-up
- 8-Bit Microprocessor
- (Optional) 16-Bit Microprocessor
- Memory-Mapped Video Display Board
- Disk Controller
- Standard Disk Hard
- (Optional) 256K RAM
- 10-Slot S-100 Motherboard
- 20-Amp Power Supply
- 12" Monitor
- Standard Intelligent 62-Key AEGON Keyboard (Optional Intelligent 88-Key AEGON Extended Keyboard)
- 100-Column Dot-Matrix Printer
- CP/M® Operating System

**You Read It Right...  
All for \$5995!**

**IMSAI**...Thinking ahead for the 80's

415/635-7615

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910 01st Avenue, Suite 14 • Oakland, CA 94621

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1980s

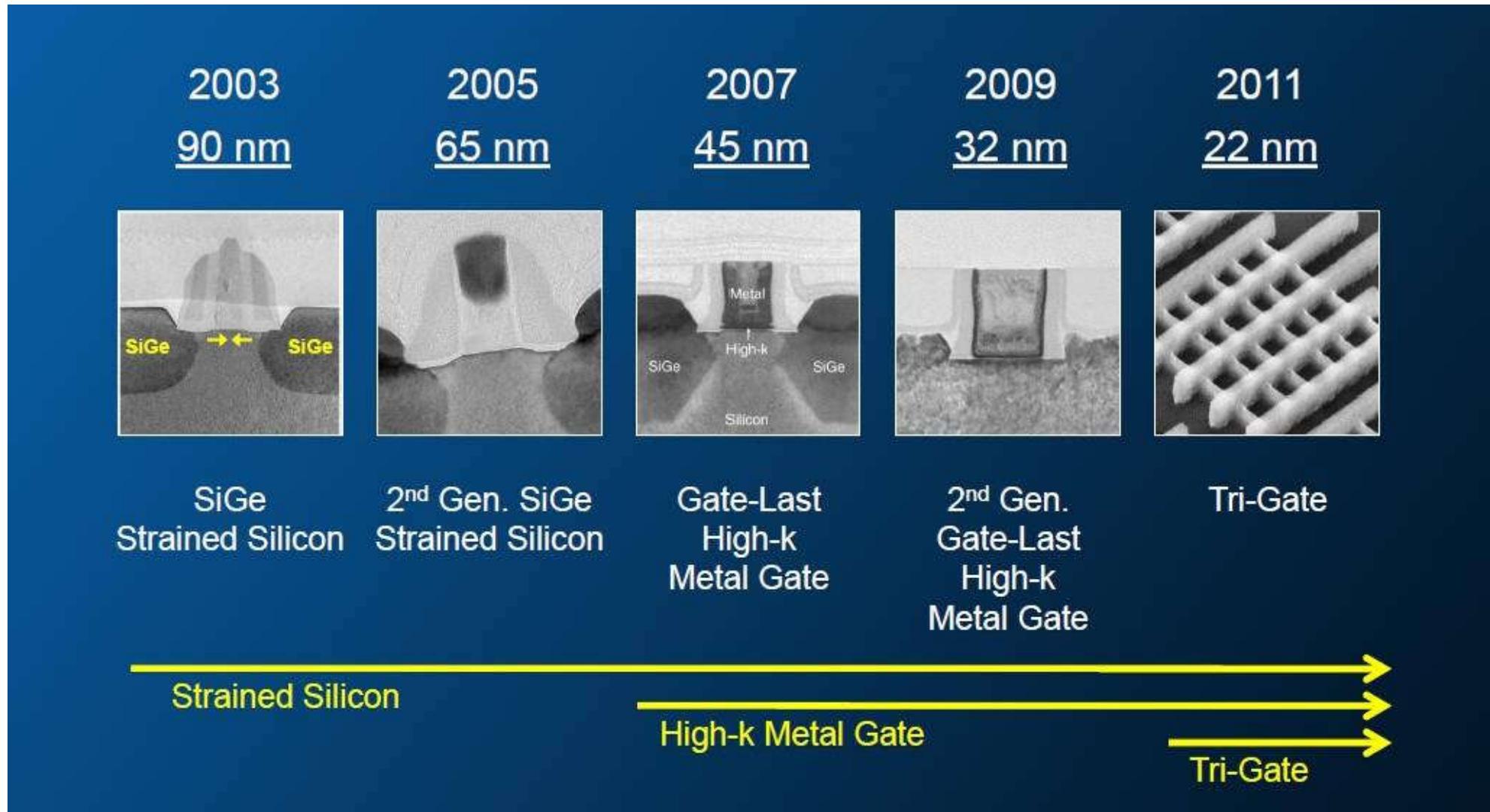


¥2549.00

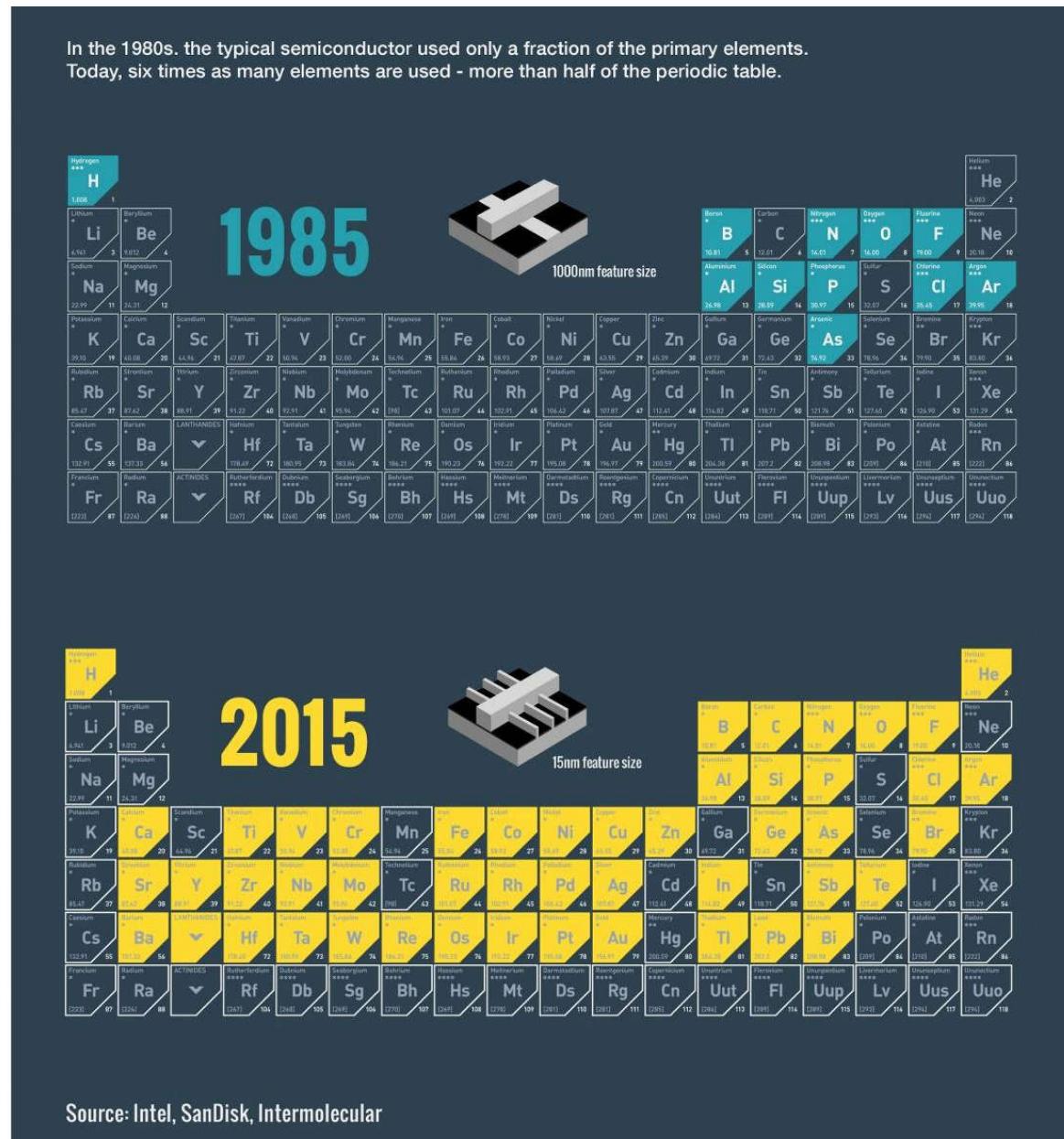
英特尔 ( Intel ) 酷睿四核 I7-7700k 盒装  
CPU 处理器 采用 Kabylake 架构 , LGA 1151

2017, price > gold

# Transistor Evolution



# Materials in IC



# Modern IC foundry



Global Foundries

*Cost > 10 billion \$\$\$*

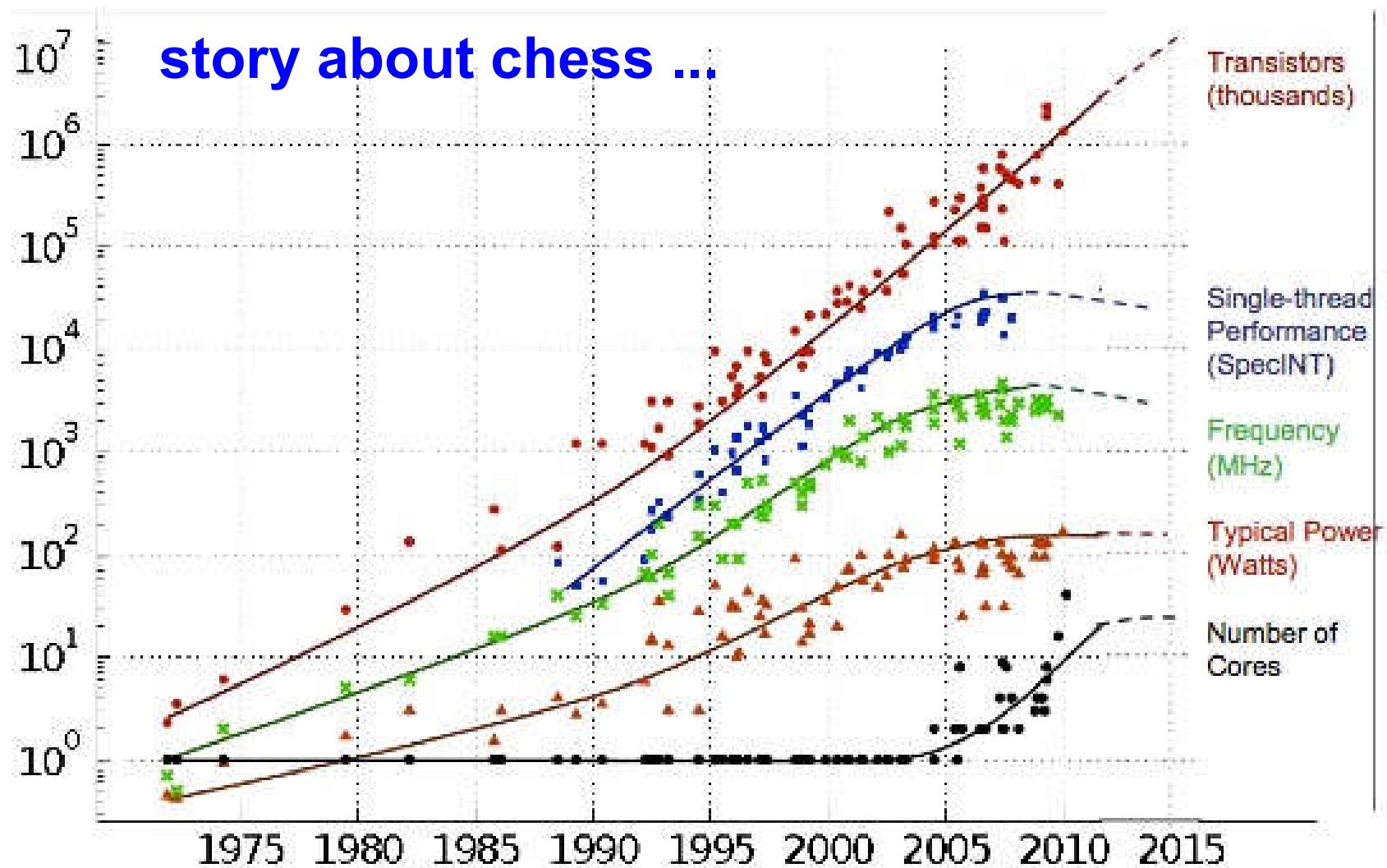
Video 1

Video 2 Intel



Samsung

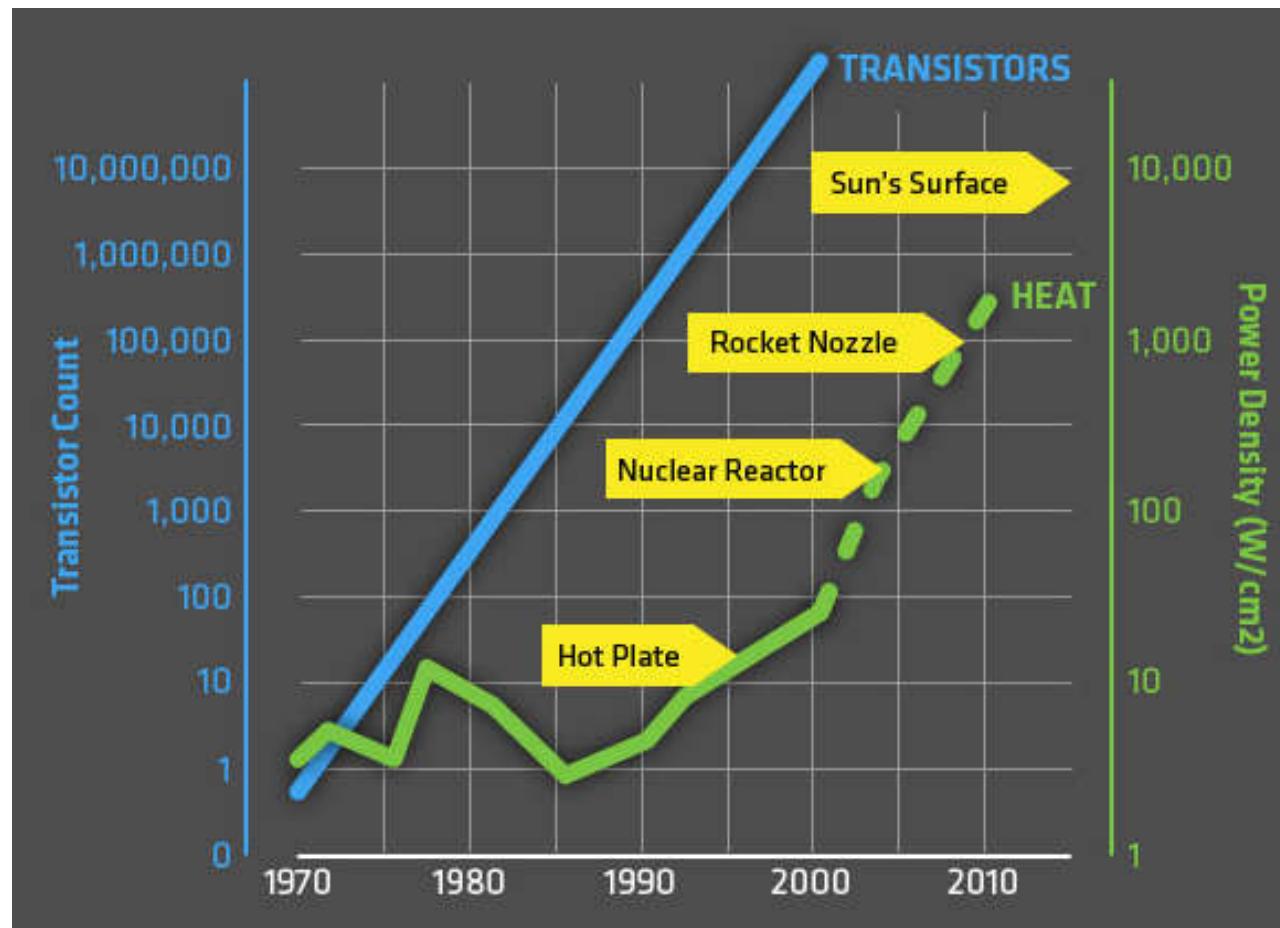
# All Good Things Come to an End



Original data collected and plotted by M. Horowitz, F. Labonte, O. Shacham, K. Olukotun, L. Hammond and C. Batten  
Dotted line extrapolations by C. Moore

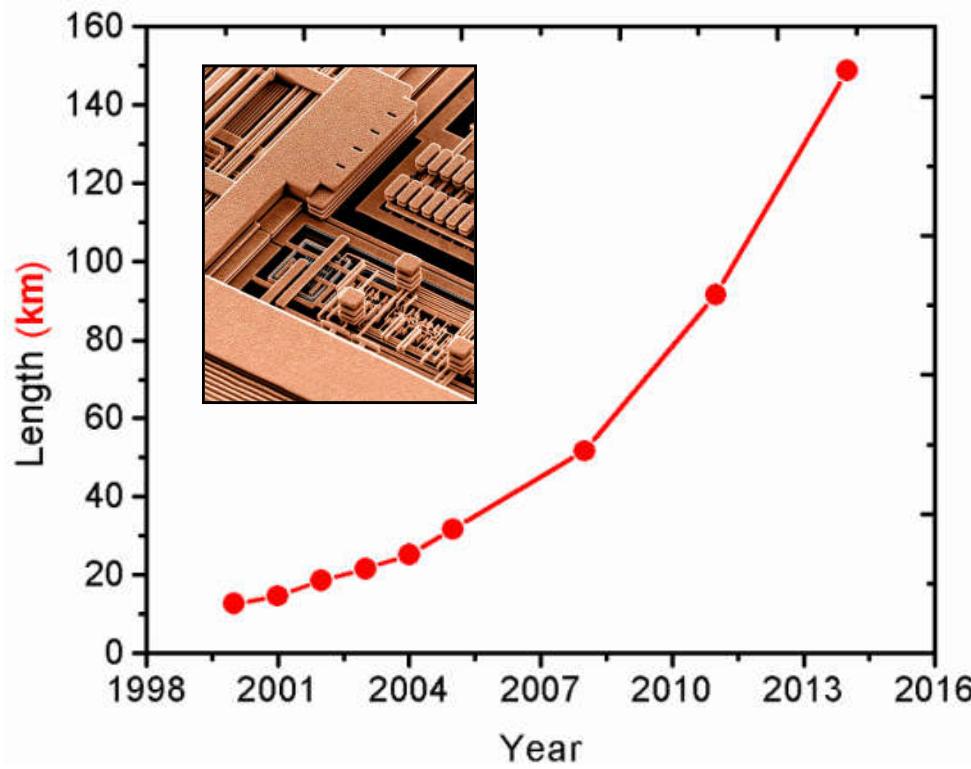
# Power Consumptions

***Shannon-von Neumann-Landauer (SNL) limit:  
minimum energy per bit  $\sim k_B T^* \ln(2)$***

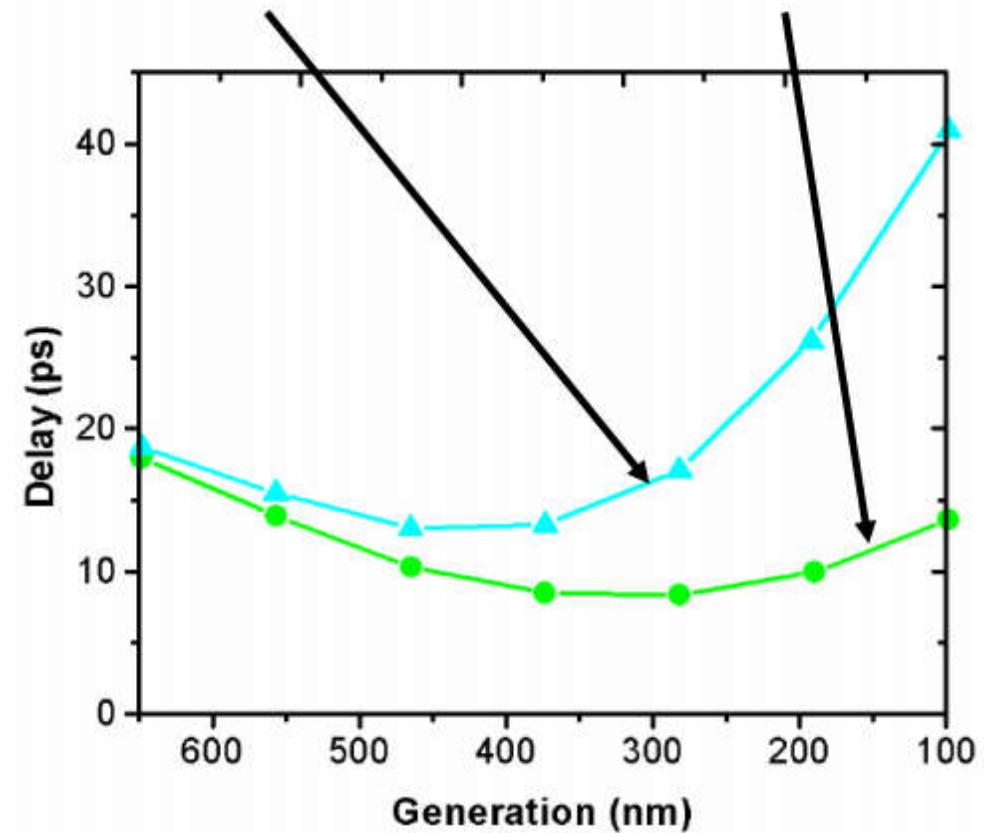


# IC Delays

$$t \sim RC$$



**total delay  
for Al/SiO<sub>2</sub>**

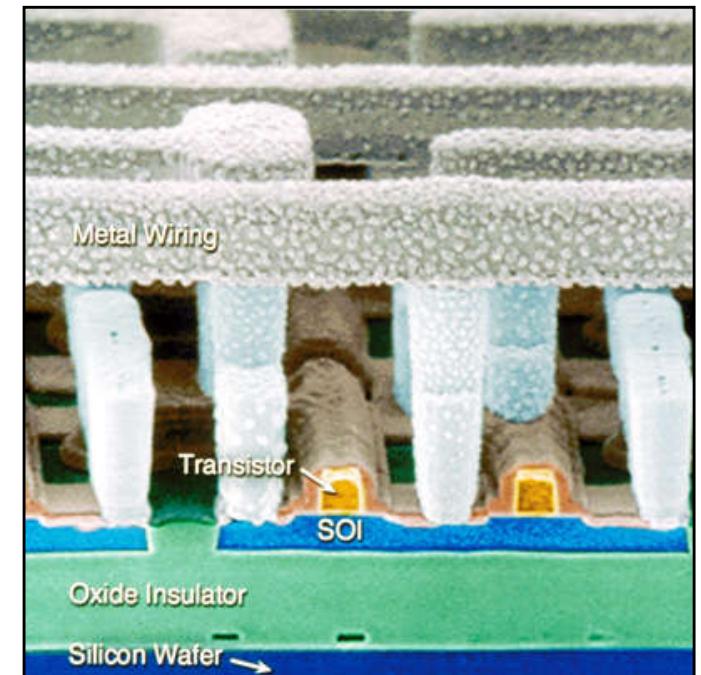


**more conductive electrodes, lower  $k$  dielectrics**

# Doping in Nano Devices

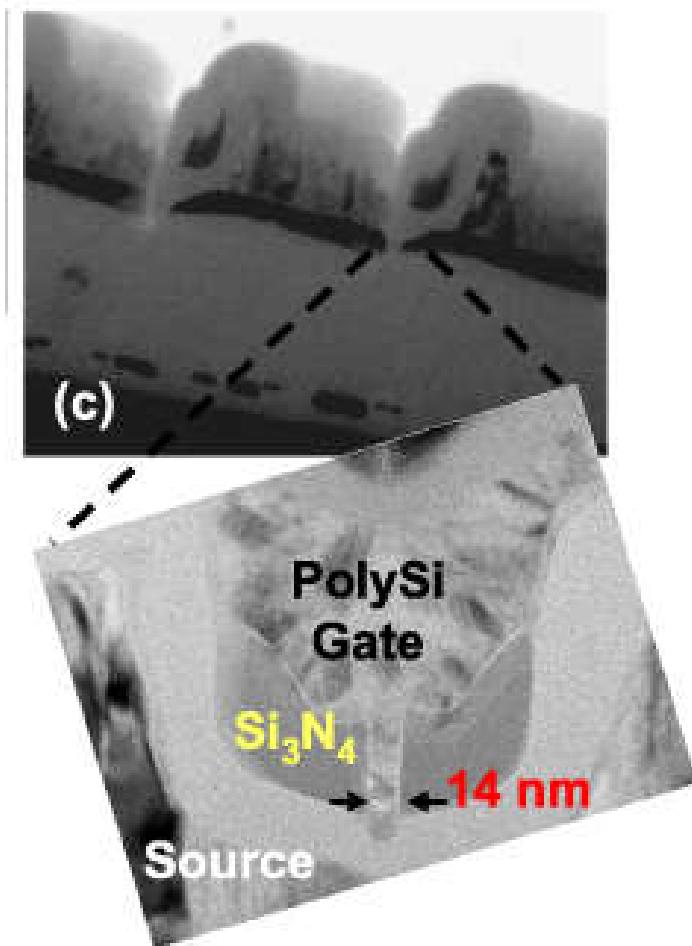
***atomic density of Si =  $5 * 10^{22} /cm^3$***

if the transistor size is  
**10 nm \* 10 nm \* 10 nm,**  
and doping concentration is  
 **$1 * 10^{18} /cm^3$**



***There is only 1 dopant atom in the transistor!***

# Grain Sizes in Nano Transistors

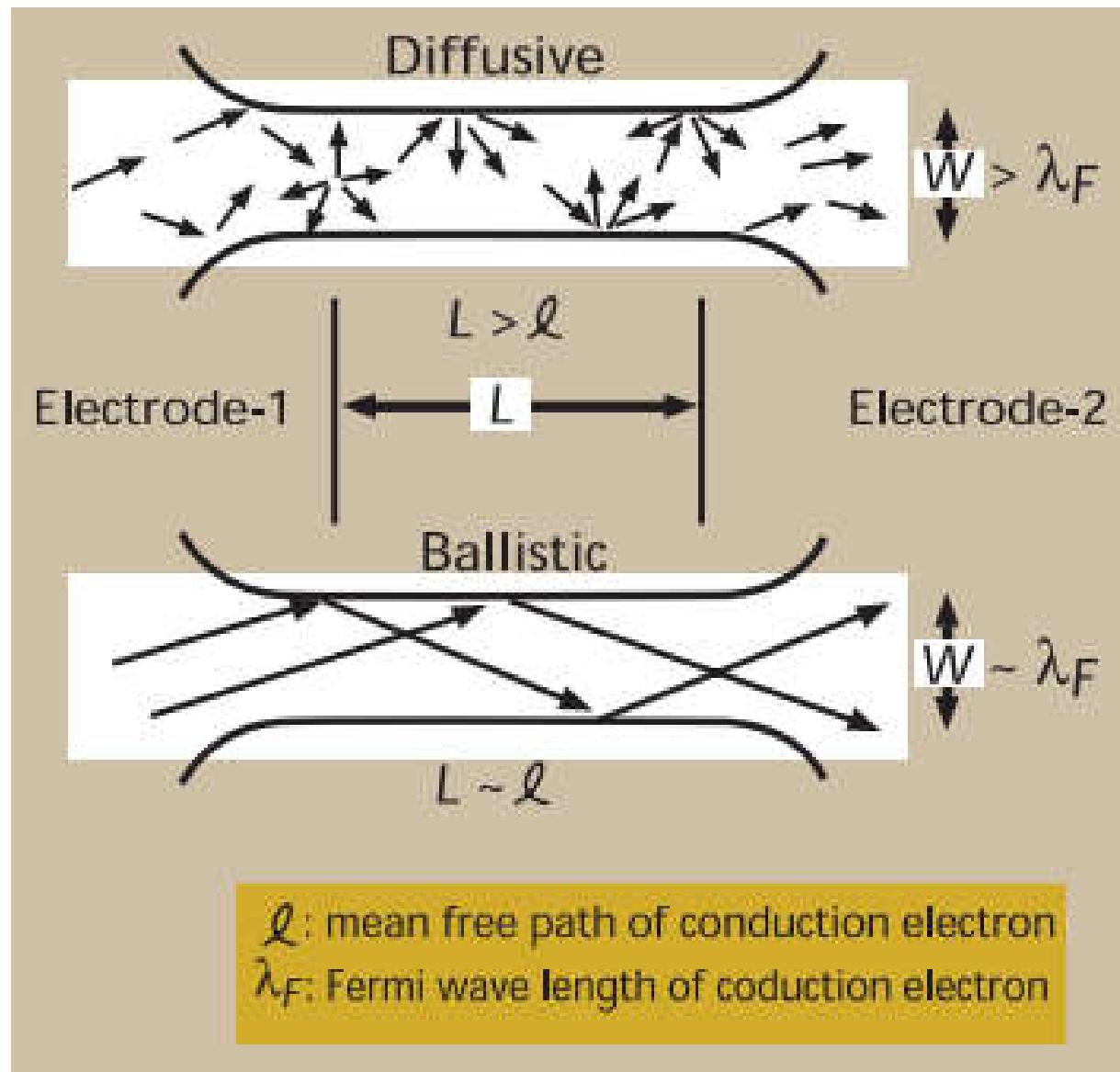


**grain size ~ a few nm**



***grain boundary, roughness,  
increased electron scattering, ...***

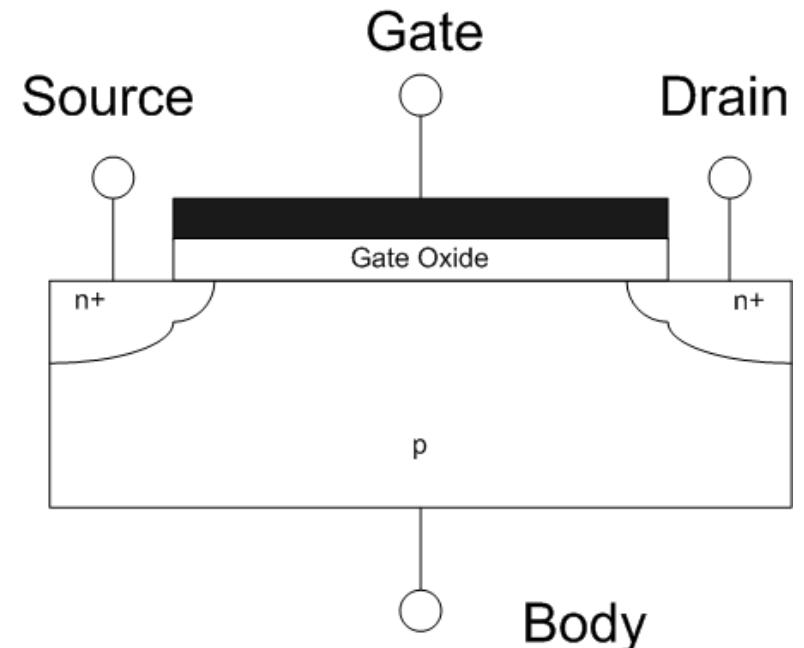
# Carrier Transport



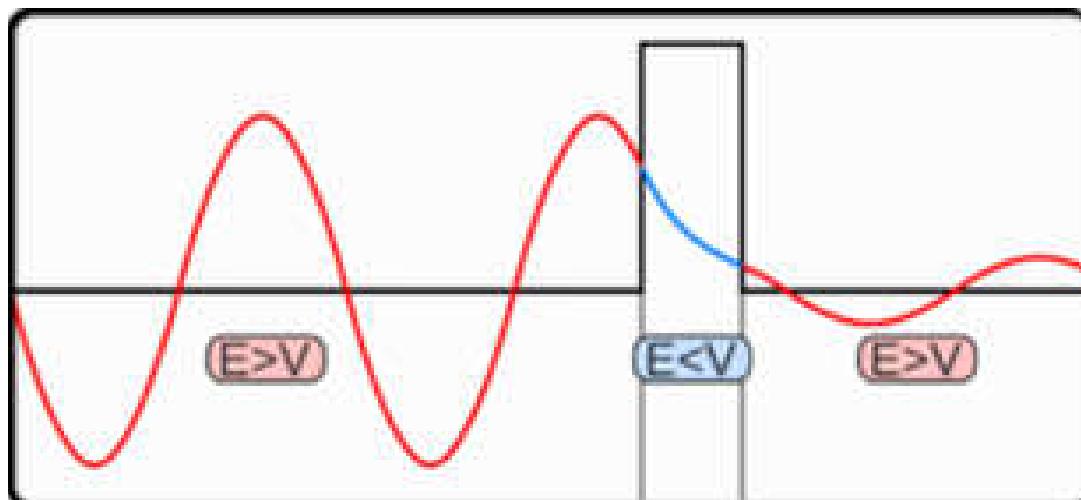
# Carrier Transport

$$I_{D,Sat} = \frac{W}{L} \mu C \frac{(V_G - V_{th})^2}{2}$$

$$C = \frac{\kappa \epsilon_0 A}{t}$$

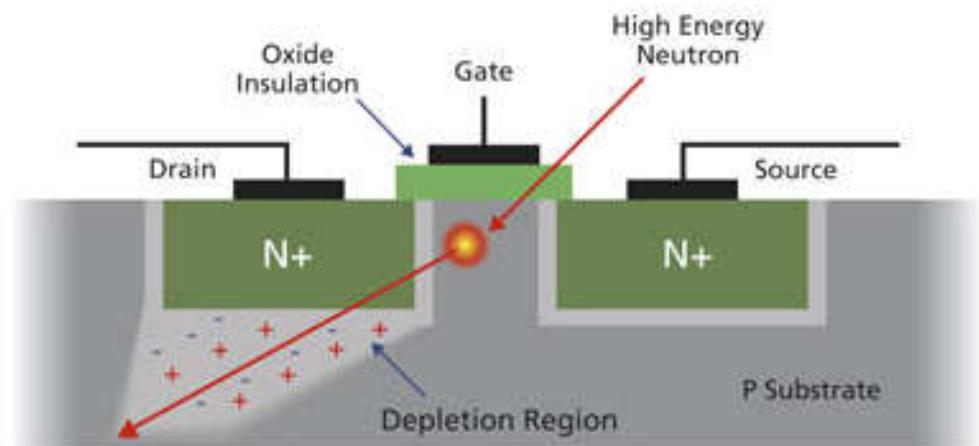
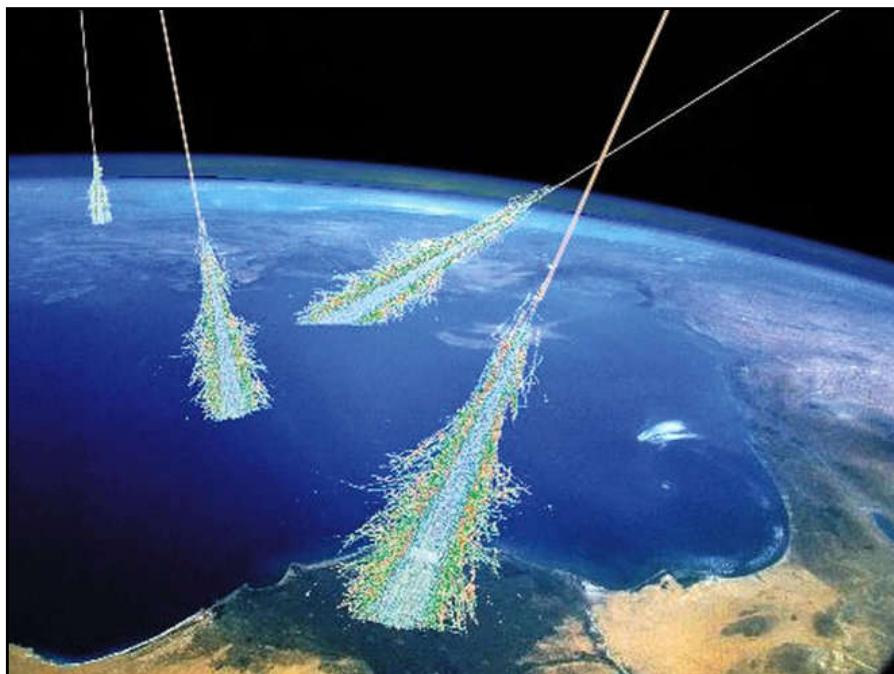


**large C requires small t**



**quantum  
tunneling**

# Danger from Outer Space



***smaller devices are more susceptible to cosmic rays***

# All Good Things Come to an End

144 | NATURE | VOL 530 | 11 FEBRUARY 2016  
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**FEATURE NEWS**

## THE SEMICONDUCTOR INDUSTRY WILL SOON ABANDON ITS PURSUIT OF MOORE'S LAW. NOW THINGS COULD GET A LOT MORE INTERESTING.

City. The Semiconductor Industry Association (SIA) in Washington DC, which represents all the major US firms, has already said that it will cease its participation in the road-mapping effort once the report is out, and will instead pursue its own research and development agenda.

Everyone agrees that the twilight of Moore's law will not mean the end of progress. "Think about what happened to airplanes," says Reed. "A Boeing 787 doesn't go any faster than a 707 did in the 1950s — but they are very different airplanes", with innovations ranging from fully electronic controls to a carbon-fibre fuselage. That's what will happen with computers, he says: "Innovation will absolutely continue — but it will be more nuanced and complicated."

**LAYING DOWN THE LAW**

The 1965 essay<sup>1</sup> that would make Gordon Moore famous started with a meditation on what could be done with the still-new technology of integrated circuits. Moore, who was then research director of Fairchild

M. M. Waldrop, *Nature* 530, 144 (2016)

# New Opportunities

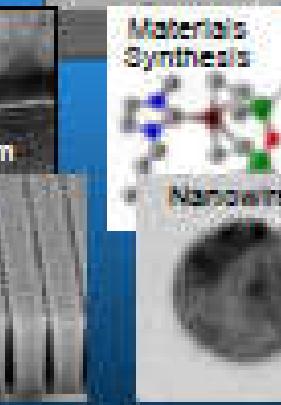
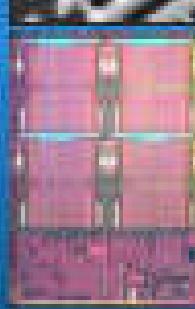
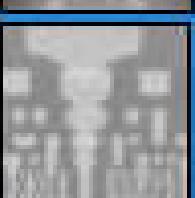
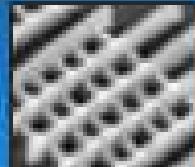
We Expect Technology Innovation to Continue

65nm  
200545nm  
200732nm  
200922nm  
2011\*14nm  
2013\*10nm  
2015\*7nm  
2017\*Beyond  
2019+

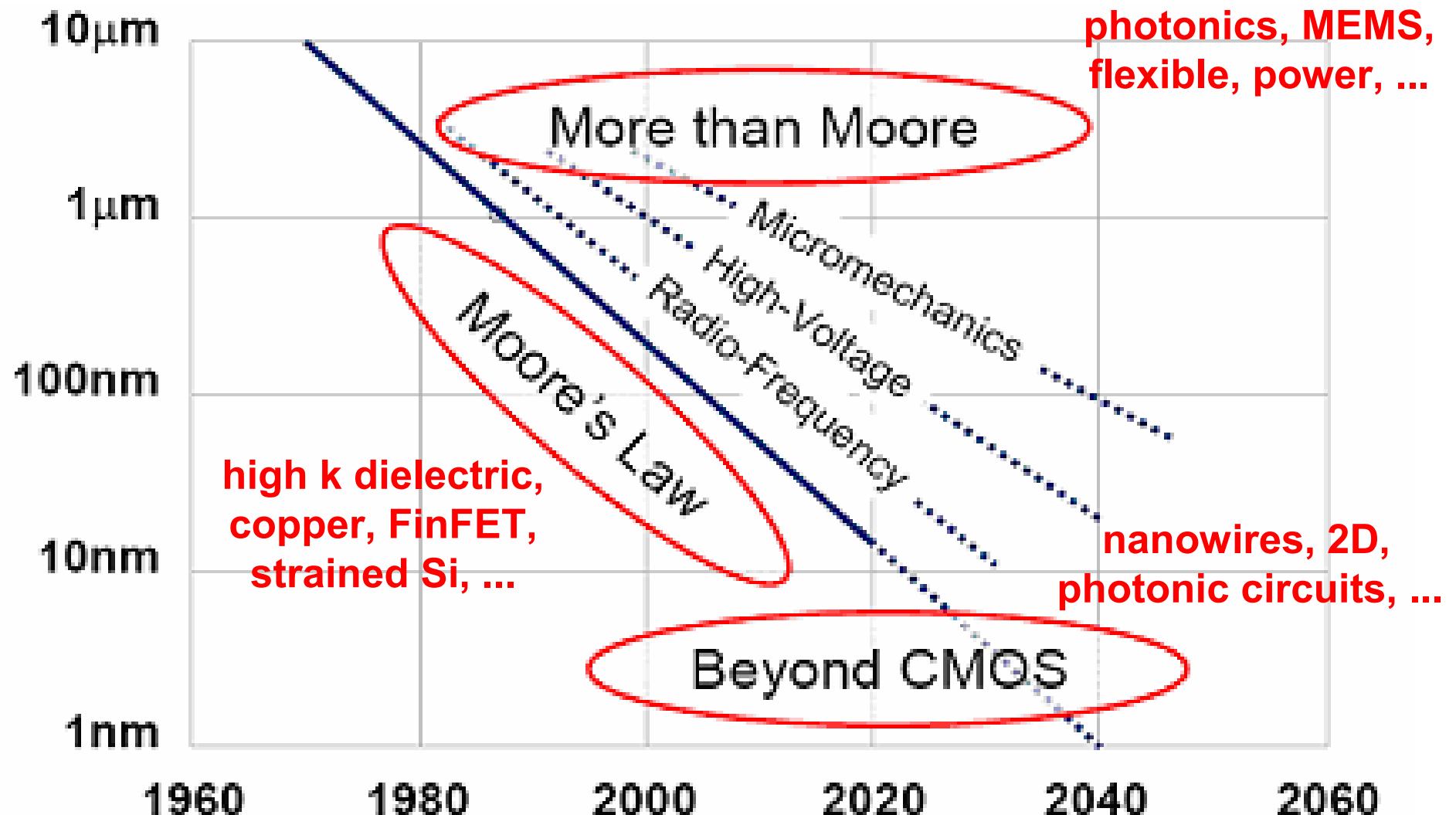
MANUFACTURING

DEVELOPMENT

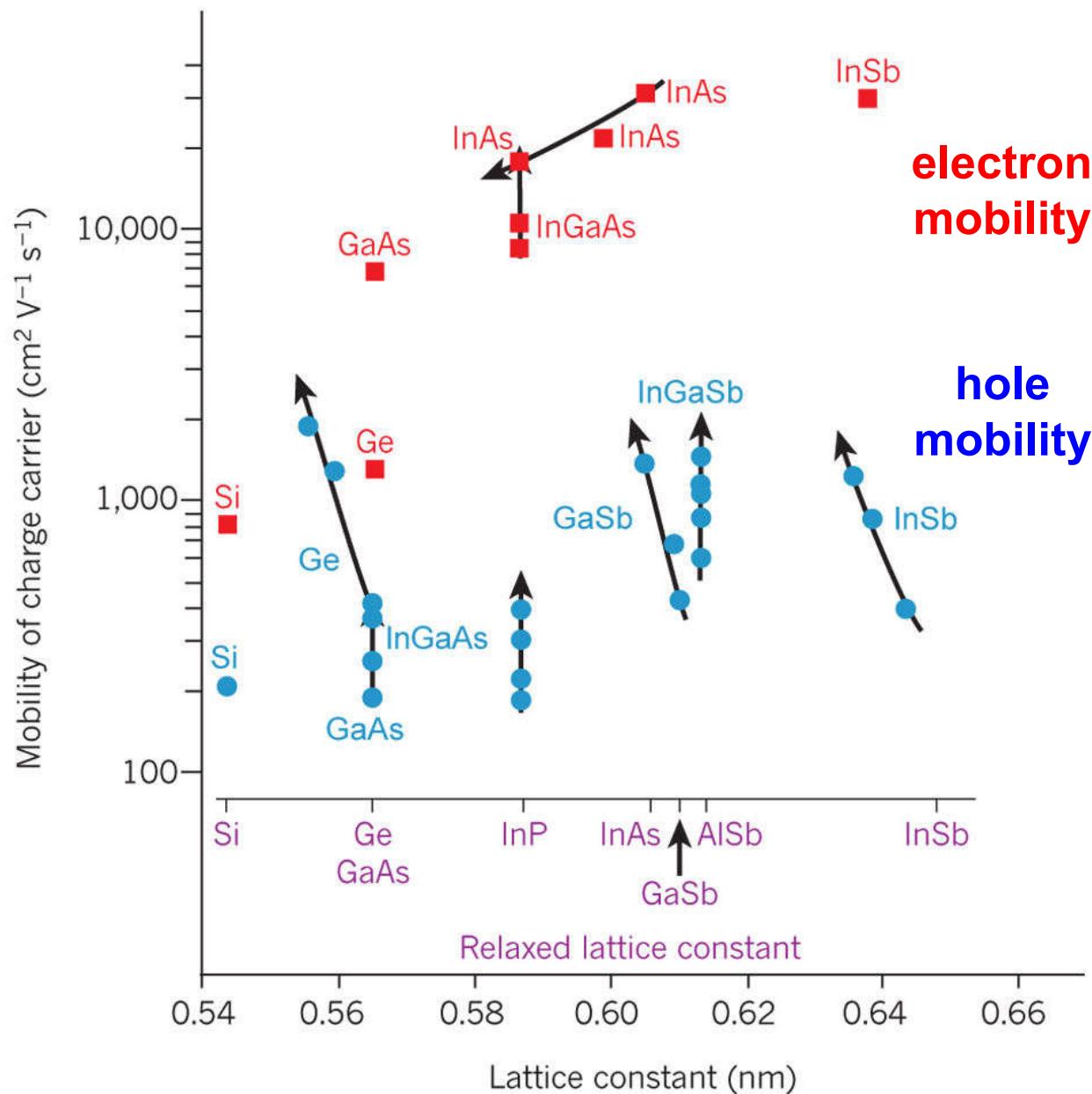
RESEARCH



# New Opportunities



# High Electron Mobility Transistor (HEMT)

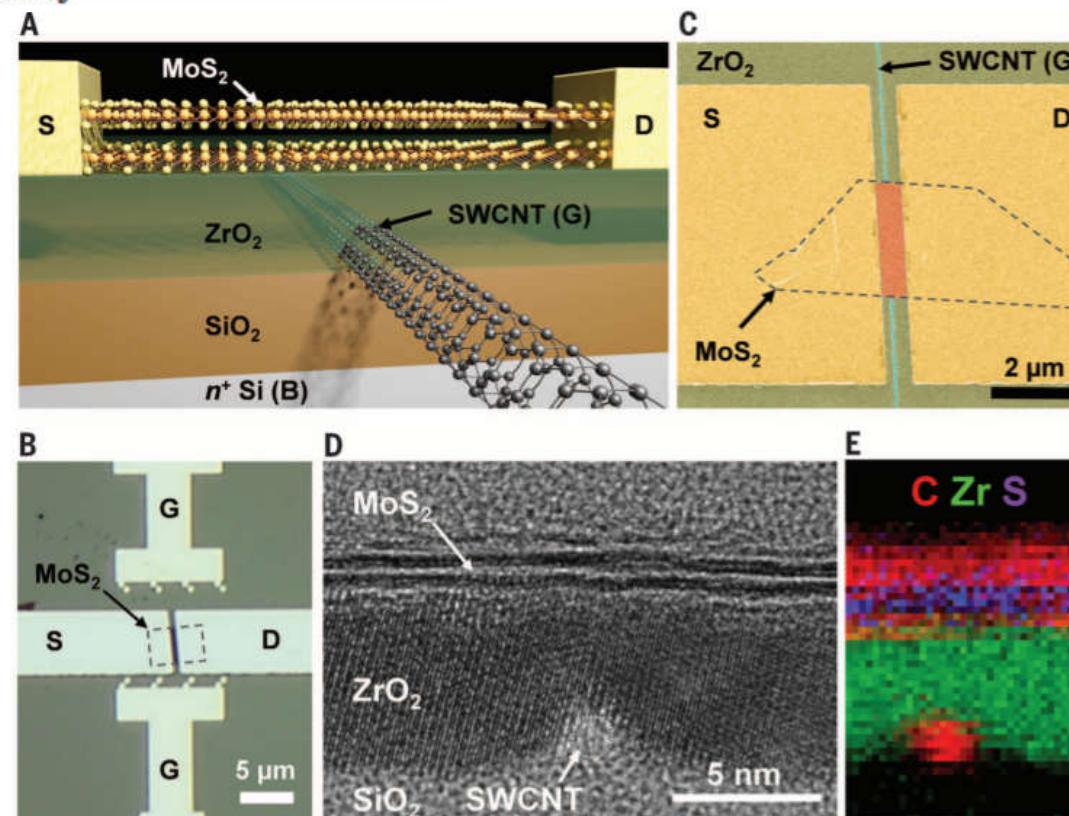


# Nano-Transistors

## DEVICE TECHNOLOGY

### **MoS<sub>2</sub> transistors with 1-nanometer gate lengths**

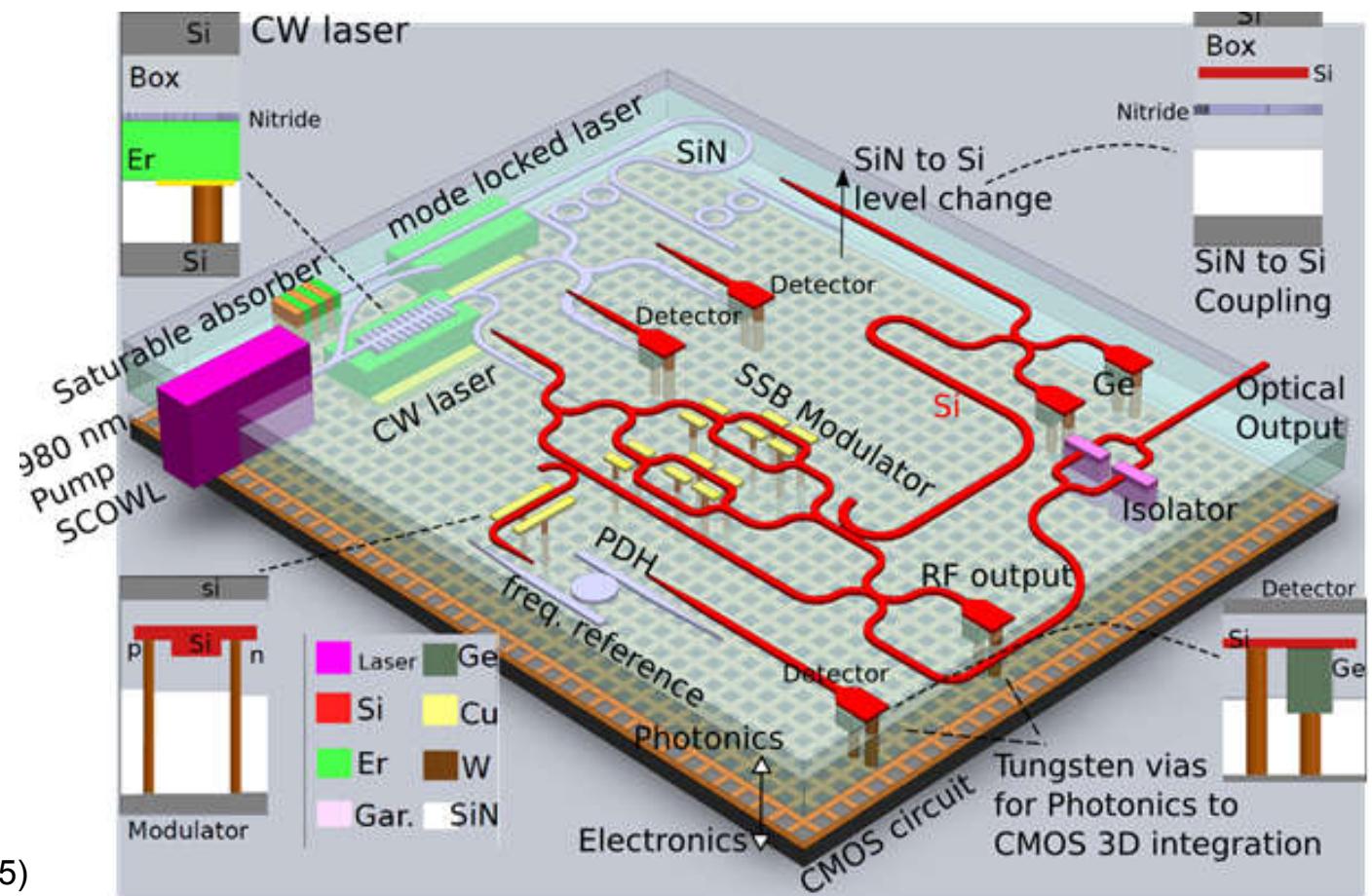
Sujay B. Desai,<sup>1,2,3</sup> Surabhi R. Madhvapathy,<sup>1,2</sup> Angada B. Sachid,<sup>1,2</sup>  
 Juan Pablo Llinas,<sup>1,2</sup> Qingxiao Wang,<sup>4</sup> Geun Ho Ahn,<sup>1,2</sup> Gregory Pitner,<sup>5</sup> Moon J. Kim,<sup>4</sup>  
 Jeffrey Bokor,<sup>1,2</sup> Chenming Hu,<sup>1</sup> H.-S. Philip Wong,<sup>5</sup> Ali Javey<sup>1,2,3\*</sup>



# Photonic Integrated Circuits

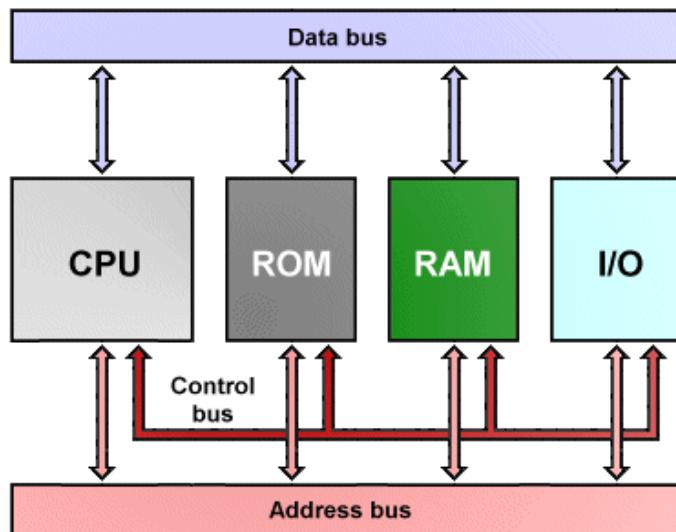
Single-chip microprocessor that communicates directly using light

Chen Sun<sup>1,2\*</sup>, Mark T. Wade<sup>3\*</sup>, Yunsup Lee<sup>1\*</sup>, Jason S. Orcutt<sup>2†\*</sup>, Luca Alloatti<sup>2</sup>, Michael S. Georgas<sup>2</sup>, Andrew S. Waterman<sup>1</sup>, Jeffrey M. Shainline<sup>3†</sup>, Rimas R. Avizienis<sup>1</sup>, Sen Lin<sup>1</sup>, Benjamin R. Moss<sup>2</sup>, Rajesh Kumar<sup>3</sup>, Fabio Pavanello<sup>3</sup>, Amir H. Atabaki<sup>2</sup>, Henry M. Cook<sup>1</sup>, Albert J. Ou<sup>1</sup>, Jonathan C. Leu<sup>2</sup>, Yu-Hsin Chen<sup>2</sup>, Krste Asanović<sup>1</sup>, Rajeev J. Ram<sup>2</sup>, Miloš A. Popović<sup>3</sup> & Vladimir M. Stojanović<sup>1</sup>

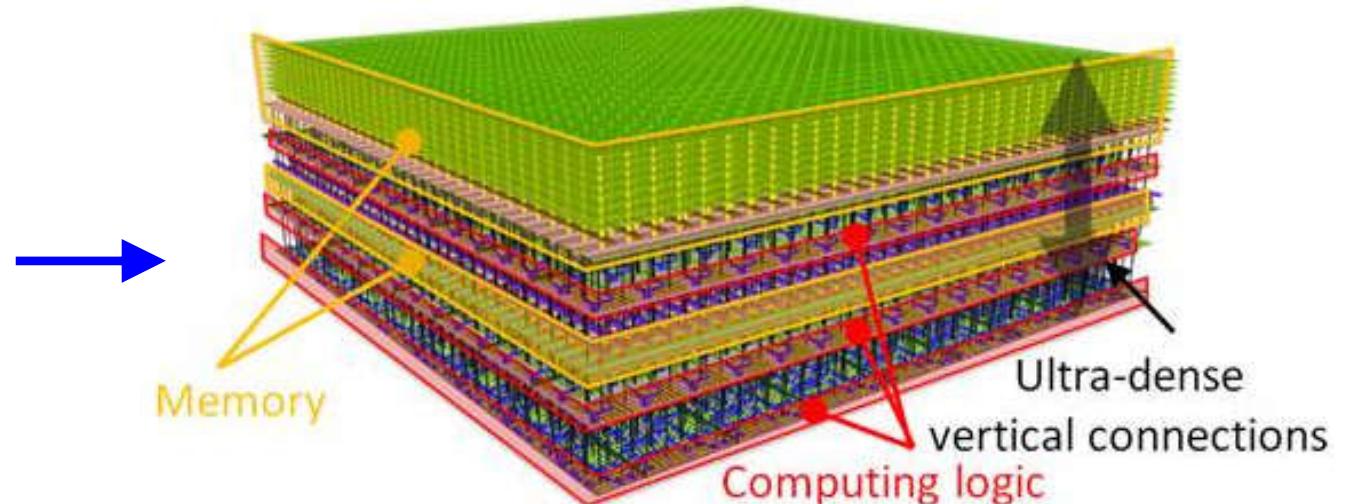


# 3D IC

- Logic + Memory + Sensing + ...

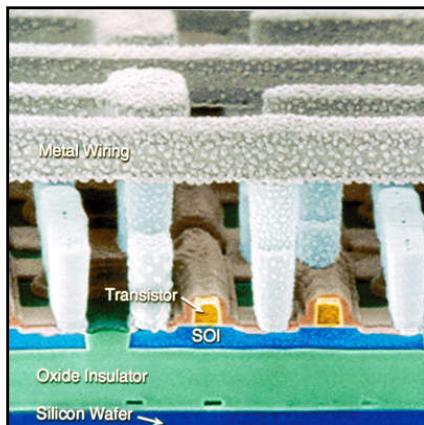


conventional

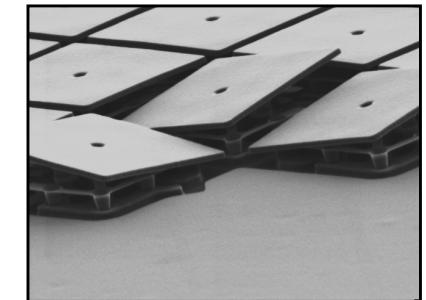
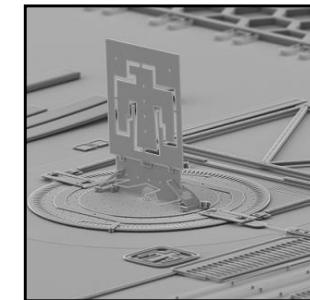
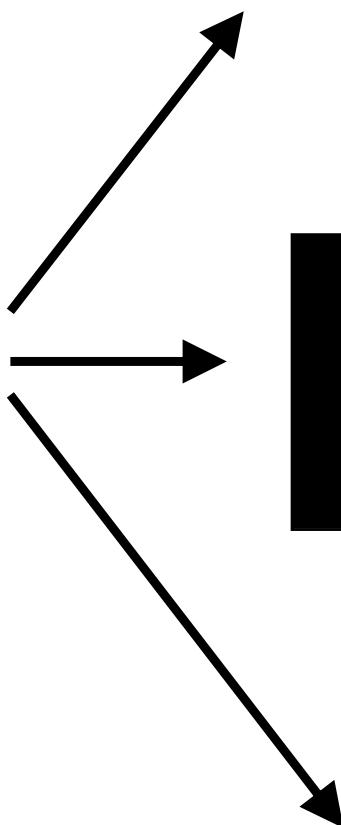


3D IC

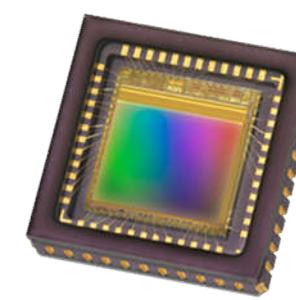
# More than Moore



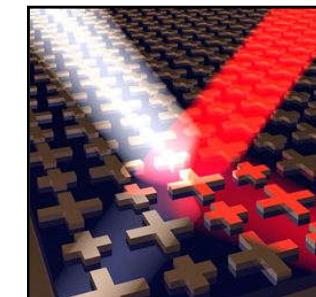
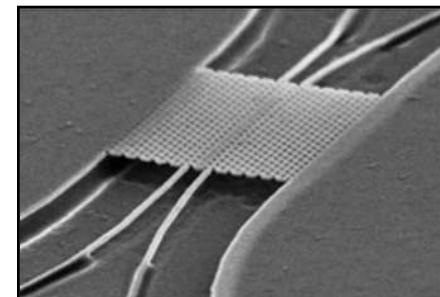
**Microelectronics**



**Microelectromechanical Systems (MEMS)**

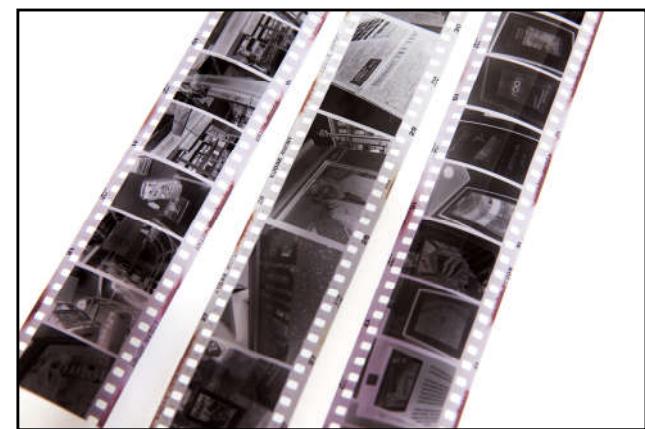


**Optoelectronics**

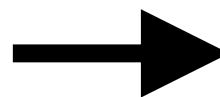


**Micro and Nano Photonics**

# Image Sensors



films



Anatomy of the Active Pixel Sensor Photodiode

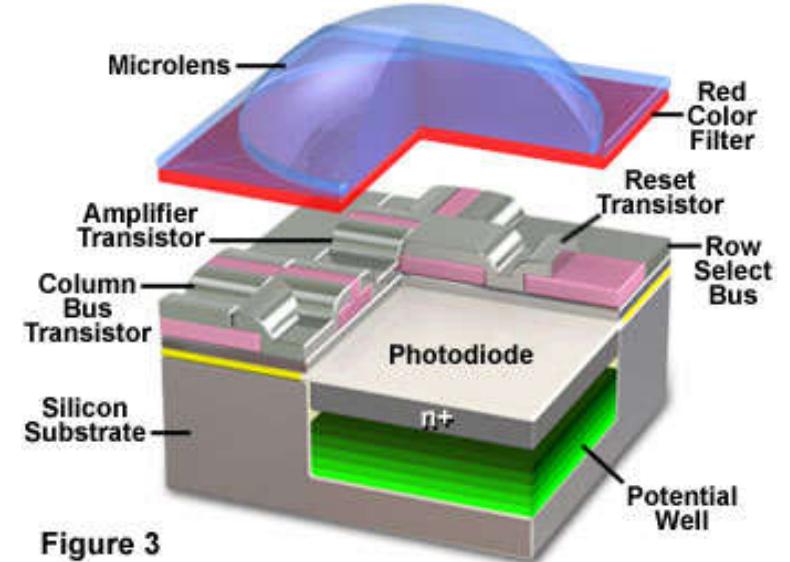
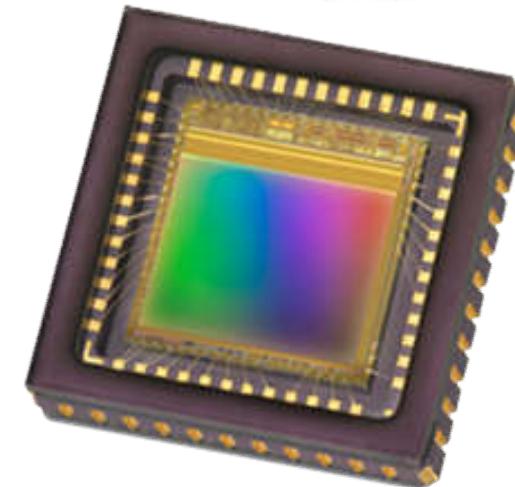
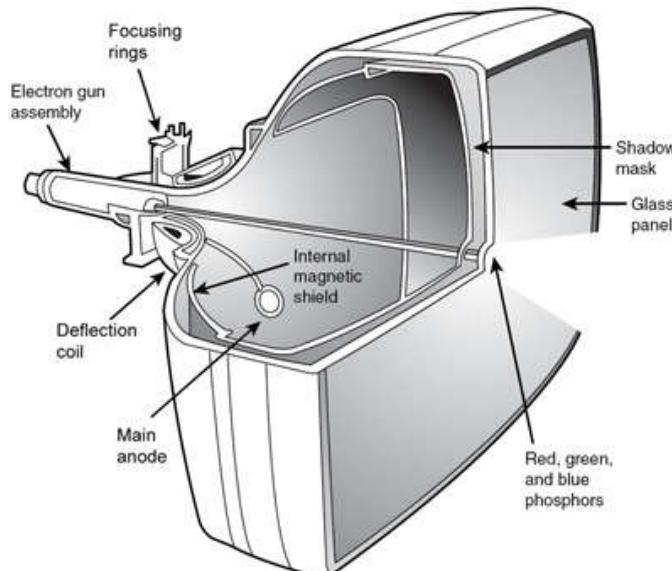


Figure 3

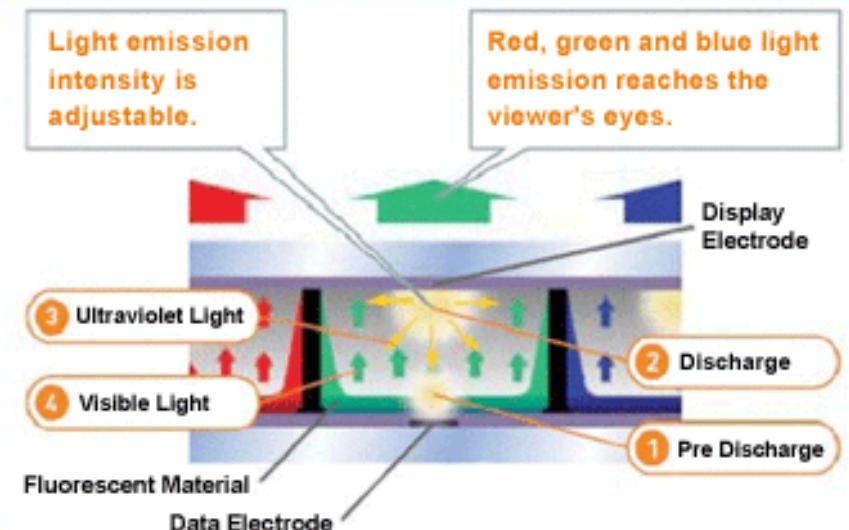
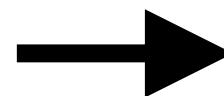


CMOS sensors

# Displays



CRT

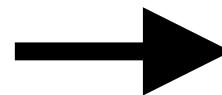


Flat panel

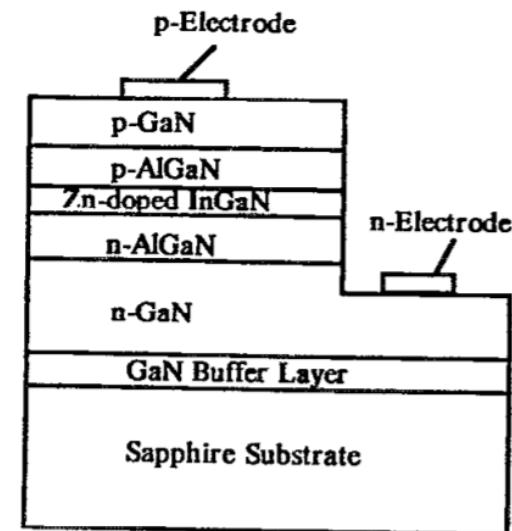
# Light Sources



Incandescent bulb



Fluorescent lamp

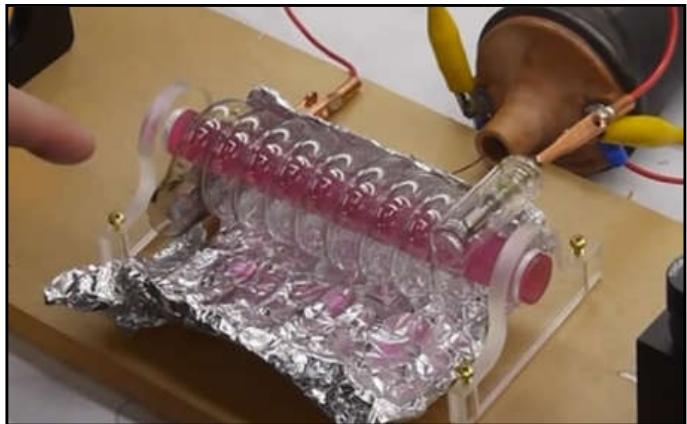


S. Nakamura, et al., *Appl. Phys. Lett.* **64**, 1687 (1994)



LEDs

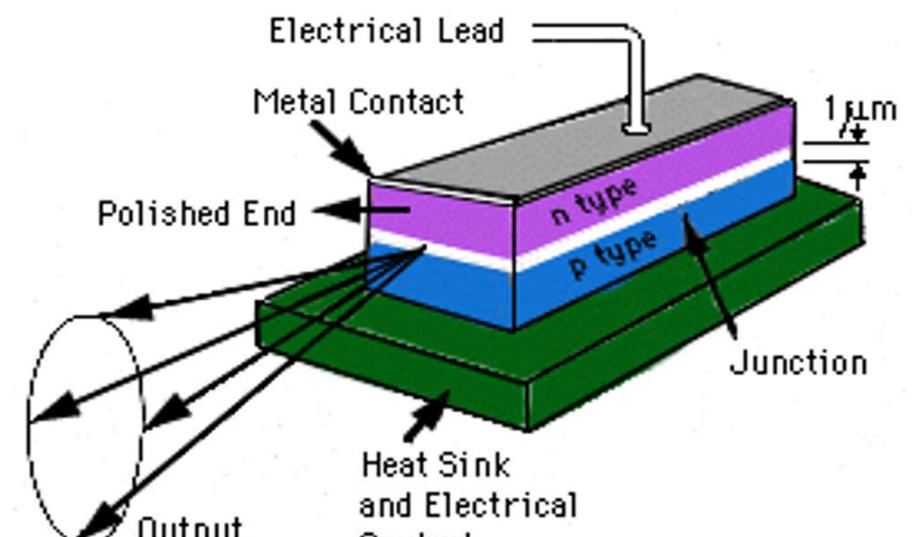
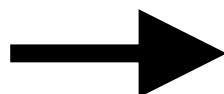
# Light Sources



**ruby laser**



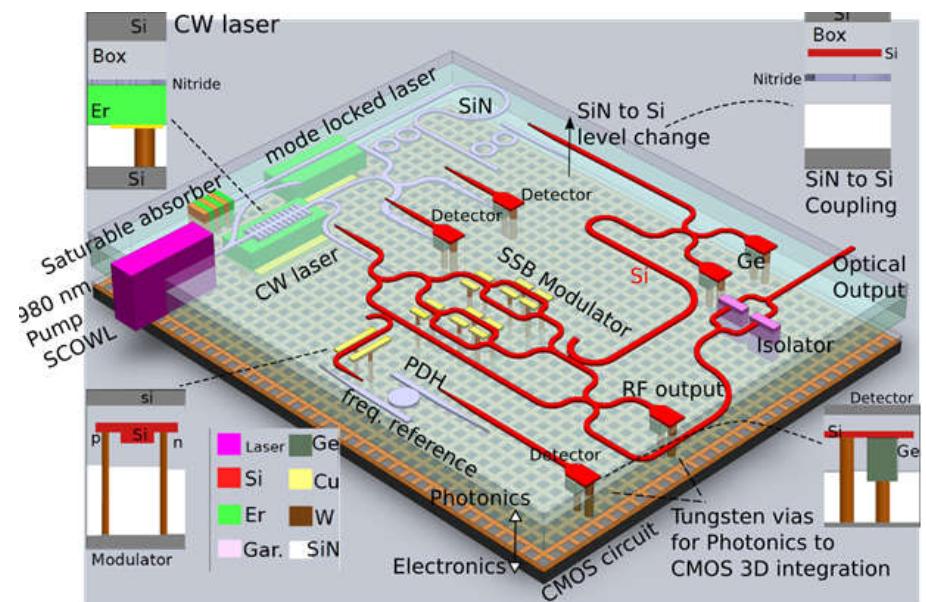
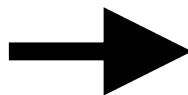
**gas laser**



**Diagram of Semiconductor Laser**

**semiconductor laser**

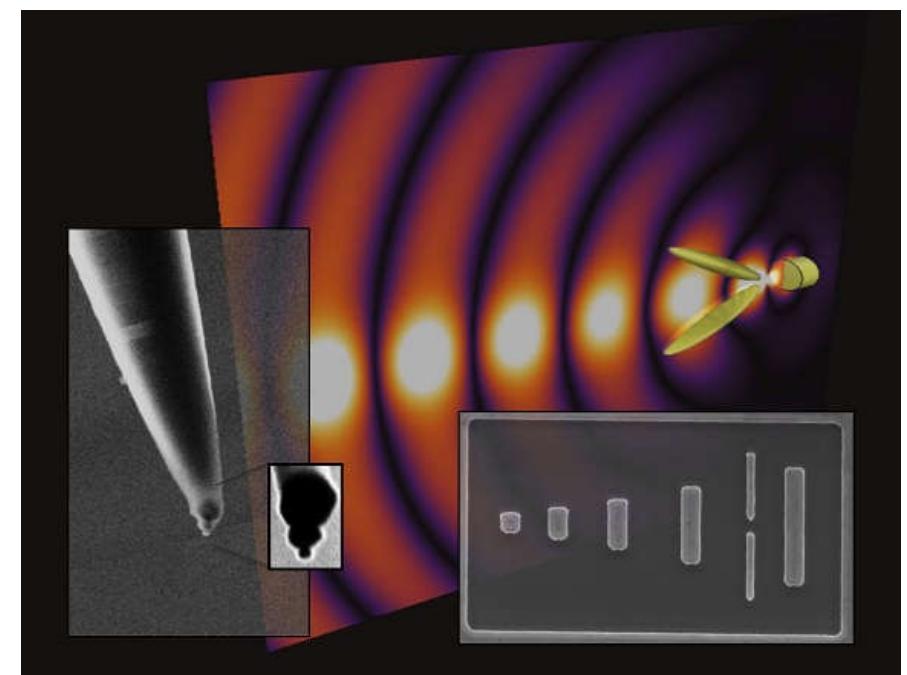
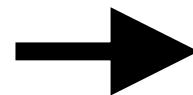
# Integrated Photonic Circuits



Conventional optics

Integrated photonics

# Integrated Photonic Circuits



Microwave Antenna

Optical Antenna